



Enhanced Low Dose Rate Sensitivity (ELDRS) Radiation Testing of the RH1573MJ8 Low Dropout PNP Regulator Driver for Linear Technology

Customer: Linear Technology (PO# 49796L)

RAD Job Number: 08-125

Part Type Tested: Linear Technology RH1573MJ8 Low Dropout PNP Regulator Driver

Commercial Part Number: RH1573K DICE. RH1573K DICE is assembled in CERDIP-8 package for testing purposes.

Traceability Information: Fab Lot# W10809524.1, Wafer 6, Assembly lot# A21534.1 (Obtained from Linear Technology PO 49796L). See photograph of unit under test in Appendix A.

Quantity of Units: 11 units total, 5 units for biased irradiation, 5 units for unbiased irradiation and 1 control unit. Serial numbers 1-5 were biased during irradiation, serial numbers 6-10 were unbiased during irradiation and serial number 22 was used as the control. See Appendix B for the radiation bias connection table.

External Traveler: None Required

Pre-Irradiation Burn-In: Burn-In performed by Linear Technology prior to receipt by RAD.

TID Dose Rate and Test Increments: 10mrad(Si)/s with readings at pre-irradiation, 10, 20, 30 and 50krad(Si).

TID Overtest and Post-Irradiation Anneal: No overtest. 24-hour room temperature anneal followed by a 168-hour 100°C anneal. Both anneals shall be performed in the same electrical bias condition as the irradiations. Electrical measurements shall be made following each anneal increment.

TID Test Standard: MIL-STD-883G, Method 1019.7, Condition D

TID Electrical Test Conditions: Pre-irradiation, and within one hour following each radiation exposure.

Test Hardware: LTS2020 Tester, 2510 Family Board, and RH1573/LT1573 BGSS-080908 DUT Board.

Facility and Radiation Source: Radiation Assured Devices Longmire Laboratories, Colorado Springs, CO using the GB-150 low dose rate Co60 source. Dosimetry performed by CaF TLDs traceable to NIST. RAD's dosimetry has been audited by DSCC and RAD has been awarded Laboratory Suitability for MIL-STD-750 TM 1019.5

Irradiation and Test Temperature: Room temperature for irradiation and test controlled to 24°C±6°C per MIL STD 883G.

ELDRS Test Result: PASSED. All parts met datasheet specifications to 50krad(Si) with only minor degradation to VREF and no significant degradation to any other measured parameter

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1.0. Overview and Background

It is well known that total dose ionizing radiation can cause parametric degradation and ultimately functional failure in electronic devices. The damage occurs via electron-hole pair production, transport and trapping in the dielectric regions. In advanced CMOS technology nodes (0.6 μ m and smaller) the bulk of the damage is manifested in the thicker isolation regions, such as shallow trench or local oxidation of silicon (LOCOS) oxides (also known as “birds-beak” oxides). However, many linear and mixed signal devices that utilize bipolar minority carrier elements exhibit an enhanced low dose rate sensitivity (ELDRS). At this time there is no known or accepted *a priori* method for predicting susceptibility to ELDRS or simulating the low dose rate sensitivity with a “conventional” room temperature 50-300rad(Si)/s irradiation (Condition A in MIL-STD-883G TM 1019.7). Over the past 10 years a number of accelerating techniques have been examined, including an elevated temperature anneal, such as that used for MOS devices (see ASTM-F-1892 for more technical details) and irradiating at various temperatures. However, none of these techniques have proven useful across the wide variety of linear and/or mixed signal devices used in spaceborne applications.

The latest requirement incorporated in MIL-STD-883G TM 1019.7 requires that devices that could potentially exhibit ELDRS “shall be tested either at the intended application dose rate, at a prescribed low dose rate to an overtest radiation level, or with an accelerated test such as an elevated temperature irradiation test that includes a parameter delta design margin”. While the recently released MIL-STD-883 TM 1019.7 allows for accelerated testing, the requirements for this are to essentially perform a low dose rate ELDRS test to verify the suitability of the acceleration method on the component of interest before the acceleration technique can be instituted. Based on the limitations of accelerated testing and to meet the requirements of MIL-STD-883G TM 1019.7 Condition D, we have performed an ELDRS test at 10mrad(Si)/s.

2.0. Radiation Test Apparatus

The ELDRS testing described in this final report was performed using the facilities at Radiation Assured Devices’ Longmire Laboratories in Colorado Springs, CO. The ELDRS source is a GB-150 irradiator modified to provide a panoramic exposure. The Co-60 rods are held in the base of the irradiator heavily shielded by lead. During the irradiation exposures the rod is raised by an electronic timer/controller and the exposure is performed in air. The dose rate for this irradiator in this configuration ranges from approximately 1mrad(Si)/s to a maximum of approximately 50rad(Si)/s as determined by the distance from the source. For the low dose rate ELDRS testing described in this report, the devices are placed approximately 2-meters from the Co-60 rods. The irradiator calibration is maintained by Radiation Assured Devices’ Longmire Laboratories using thermoluminescent dosimeters (TLDs) traceable to the National Institute of Standards and Technology (NIST). Figure 2.1 shows a photograph of the Co-60 irradiator at RAD’s Longmire Laboratory facility.



Figure 2.1. Radiation Assured Devices' Co-60 irradiator. The dose rate is obtained by positioning the device-under-test at a fixed distance from the gamma cell. The dose rate for this irradiator varies from approximately 50rad(Si)/s close to the rods down to <1mrad(Si)/s at a distance of approximately 4-meters.



3.0. Radiation Test Conditions

The RH1573MJ8 low dropout PNP regulator driver described in this final report was tested using two bias conditions, statically biased with a 7V V_{IN} and all pins tied to ground, see Appendix A for details on biasing conditions. These devices were irradiated to a maximum total ionizing dose level of 50krad(Si) with incremental readings at 10, 20, 30 and 50krad(Si). Electrical testing occurred within one hour following the end of each irradiation segment. For intermediate irradiations, the units were tested and returned to total dose exposure within two hours from the end of the previous radiation increment. The ELDRS bias board was positioned in the Co-60 cell to provide the required 10mrad(Si)/s and was located inside a lead-aluminum box. The lead-aluminum box is required under MIL-STD-883G TM1019.7 Section 3.4 that reads as follows: “Lead/Aluminum (Pb/Al) container. Test specimens shall be enclosed in a Pb/Al container to minimize dose enhancement effects caused by low-energy, scattered radiation. A minimum of 1.5 mm Pb, surrounding an inner shield of at least 0.7 mm Al, is required. This Pb/Al container produces an approximate charged particle equilibrium for Si and for TLDs such as CaF₂. The radiation field intensity shall be measured inside the Pb/Al container (1) initially, (2) when the source is changed, or (3) when the orientation or configuration of the source, container, or test-fixture is changed. This measurement shall be performed by placing a dosimeter (e.g., a TLD) in the device-irradiation container at the approximate test-device position. If it can be demonstrated that low energy scattered radiation is small enough that it will not cause dosimetry errors due to dose enhancement, the Pb/Al container may be omitted”.

The final dose rate within the lead-aluminum box was determined based on TLD dosimetry measurements just prior to the beginning of the total dose irradiations. The final dose rate for this work was 10.0mrad(Si)/s with a precision of $\pm 5\%$.



4.0. Tested Parameters

The following parameters were tested during the course of this work:

1. Input Quiescent Current (A)
2. Reference Voltage (V)
3. Line Regulation (V)
4. Load Regulation (V)
5. FB Pin Bias Current (A)
6. DRIVE Pin Current VFB=1.35V (A)
7. DRIVE Pin Current VFB=1.15V (A)
8. DRIVE Pin Saturation Voltage ID=20mA (V)
9. DRIVE Pin Saturation Voltage ID=250mA (V)
10. SHDN Pin Threshold Voltage (V)
11. SHDN Pin Current (A)
12. LATCH Pin Latch-Off Threshold Voltage (V)
13. LATCH Pin Charging Current (A)
14. LATCH Pin Latching Current (A)
15. VIN-VOUT Diff Threshold Latch Disable (V)
16. Minimum Bias Voltage (V)

Appendix C details the measured parameters, test conditions, pre-irradiation specification and measurement resolution for each of the measurements.

The parametric data was obtained as “read and record” and all the raw data plus an attributes summary are contained in this report as well as in a separate Excel file. The attributes data contains the average, standard deviation and the average with the KTL values applied. The KTL values used is 2.742 per MIL HDBK 814 using one sided tolerance limits of 90/90 and a 5-piece sample size. This survival probability/level of confidence is consistent with a 22-piece sample size and zero failures analyzed using a lot tolerance percent defective (LTPD) approach. Note that the following criteria must be met for a device to pass the ELDRS testing: following the radiation exposure the unit shall pass the specification value and the average value for the each device must pass the specification value when the KTL limits are applied. If either of these conditions is not satisfied following the radiation exposure, then the lot could be logged as an RLAT failure.

Further, MIL-STD-883G, TM 1019.7 Section 3.13.1.1 Characterization test to determine if a part exhibits ELDRS” states the following: Select a minimum random sample of 21 devices from a population representative of recent production runs. Smaller sample sizes may be used if agreed upon between the parties to the test. All of the selected devices shall have undergone appropriate elevated temperature reliability screens, e.g. burn-in and high temperature storage life. Divide the samples into four groups of 5 each and use the remaining part for a control. Perform pre-irradiation electrical



characterization on all parts assuring that they meet the Group A electrical tests. Irradiate 5 samples under a 0 volt bias and another 5 under the irradiation bias given in the acquisition specification at 50-300 rad(Si)/s and room temperature. Irradiate 5 samples under a 0 volt bias and another 5 under irradiation bias given in the acquisition specification at < 10mrads(Si)/s and room temperature. Irradiate all samples to the same dose levels, including 0.5 and 1.0 times the anticipated specification dose, and repeat the electrical characterization on each part at each dose level. Post irradiation electrical measurements shall be performed per paragraph 3.10 where the low dose rate test is considered Condition D. Calculate the radiation induced change in each electrical parameter (Δ para) for each sample at each radiation level. Calculate the ratio of the median Δ para at low dose rate to the median Δ para at high dose rate for each irradiation bias group at each total dose level. If this ratio exceeds 1.5 for any of the most sensitive parameters then the part is considered to be ELDRS susceptible. This test does not apply to parameters which exhibit changes that are within experimental error or whose values are below the pre-irradiation electrical specification limits at low dose rate at the specification dose.

Therefore, the data in this report can be analyzed along with the high dose rate report titled “Radiation Lot Acceptance Testing (RLAT) of the RH1573MJ8 Low dropout PNP regulator driver for Linear Technology” to demonstrate that these parts do not exhibit ELDRS as defined in the current test method.

5.0. ELDRS Test Results

Using the conditions stated above, the RH1573MJ8 devices passed the ELDRS test to 50krads(Si) with no significant degradation to most of the measured parameters. Where radiation induced degradation was observed the degradation was not sufficient to cause the parameter to exceed the specification value. Note that V_{REF} exceeded the upper datasheet specification after application of the 90/90 KTL statistics due to the relative large standard deviation of the sample population compared to the very tight specification limits. In our opinion this lot of material could be qualified to 50krads(Si) using larger samples sizes and an “attributes” approach, i.e. 22 units passing with 0 failures.

Figures 5.1 through 5.16 show plots of all the measured parameters versus total ionizing dose. In the data plots the solid diamonds are the average of the measured data points for the sample irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the units irradiated with all pins tied to ground. The black lines (solid or dashed) are the average of the data points after application of the KTL statistics on the sample irradiated in the biased condition while the shaded lines (solid or dashed) are the average of the data points after application of the KTL statistics on the sample irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.

Tables 5.1 through 5.16 show the raw data, averages, standard deviation, +KTL statistics, -KTL statistics, specification limit and Pass/Fail condition for each parameter. Appendix D provides a list of all the figures in this results section to facilitate the location of a particular parameter.



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08-125 090825 R1.1**

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As seen clearly in these tables and figures, the pre- and post-irradiation data are well within the specification even after application of the KTL statistics (with certain exceptions, as noted below). The control units, as expected, show no significant changes to any of the parameters. Therefore we can conclude that the electrical testing remained under control during the course of the testing.

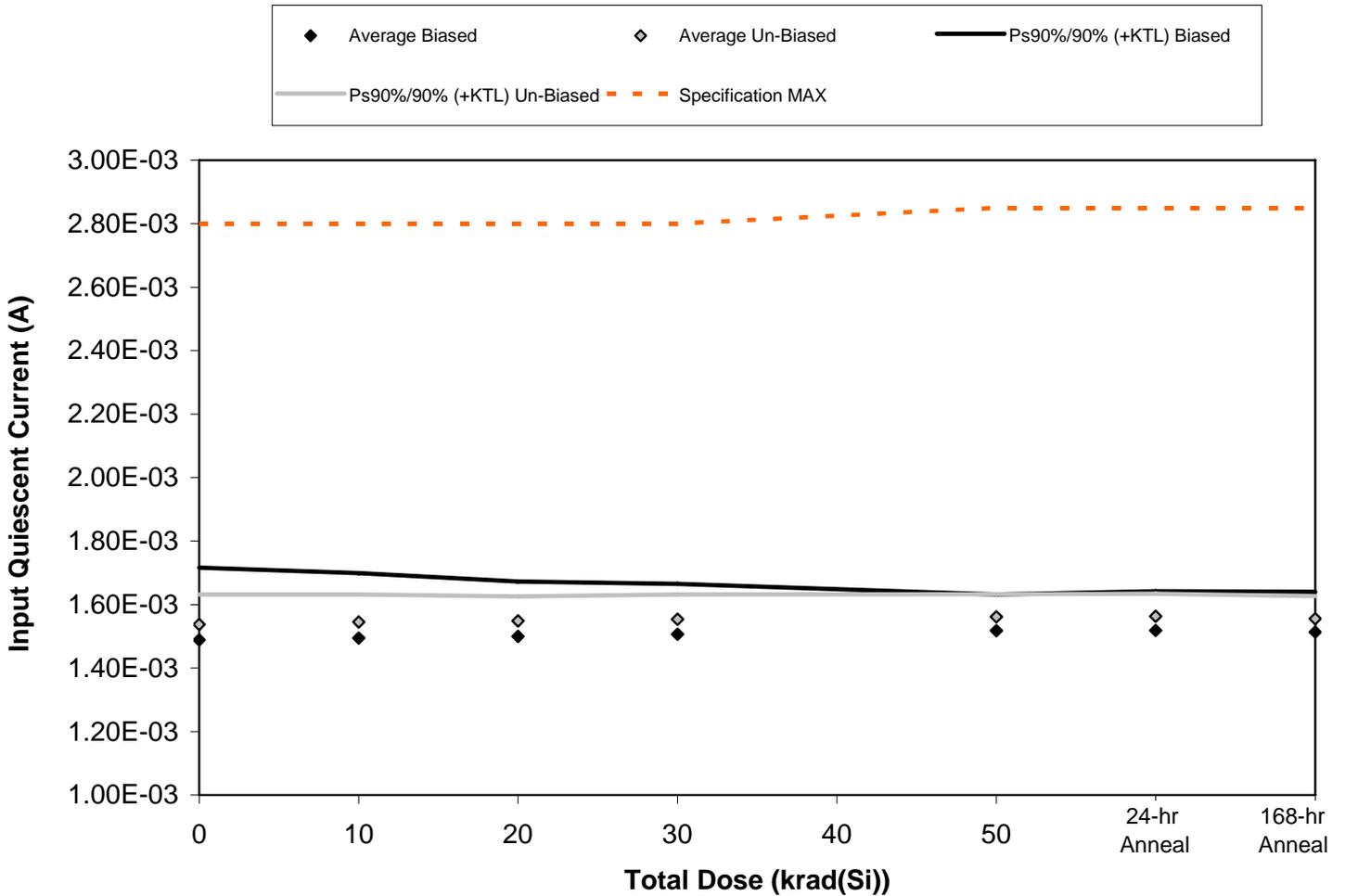


Figure 5.1. Plot of Input Quiescent Current (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.1. Raw data for Input Quiescent Current (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

Input Quiescent Current (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.53E-03	1.53E-03	1.53E-03	1.53E-03	1.53E-03	1.53E-03	1.53E-03
2	1.53E-03	1.52E-03	1.52E-03	1.53E-03	1.53E-03	1.53E-03	1.53E-03
3	1.34E-03	1.36E-03	1.39E-03	1.40E-03	1.45E-03	1.44E-03	1.43E-03
4	1.54E-03	1.54E-03	1.54E-03	1.55E-03	1.55E-03	1.55E-03	1.55E-03
5	1.51E-03	1.51E-03	1.52E-03	1.53E-03	1.54E-03	1.54E-03	1.54E-03
6	1.55E-03	1.55E-03	1.55E-03	1.55E-03	1.56E-03	1.56E-03	1.55E-03
7	1.57E-03	1.58E-03	1.58E-03	1.59E-03	1.60E-03	1.60E-03	1.59E-03
8	1.54E-03	1.55E-03	1.55E-03	1.55E-03	1.55E-03	1.56E-03	1.55E-03
9	1.55E-03	1.56E-03	1.56E-03	1.56E-03	1.57E-03	1.57E-03	1.56E-03
10	1.48E-03	1.49E-03	1.51E-03	1.51E-03	1.53E-03	1.53E-03	1.52E-03
22	1.49E-03	1.48E-03	1.49E-03	1.49E-03	1.49E-03	1.49E-03	1.49E-03
Biased Statistics							
Average Biased	1.49E-03	1.49E-03	1.50E-03	1.51E-03	1.52E-03	1.52E-03	1.51E-03
Std Dev Biased	8.31E-05	7.45E-05	6.31E-05	5.78E-05	4.15E-05	4.51E-05	4.63E-05
Ps90%/90% (+KTL) Biased	1.72E-03	1.70E-03	1.67E-03	1.66E-03	1.63E-03	1.64E-03	1.64E-03
Ps90%/90% (-KTL) Biased	1.26E-03	1.29E-03	1.33E-03	1.35E-03	1.40E-03	1.39E-03	1.39E-03
Un-Biased Statistics							
Average Un-Biased	1.54E-03	1.55E-03	1.55E-03	1.55E-03	1.56E-03	1.56E-03	1.56E-03
Std Dev Un-Biased	3.43E-05	3.16E-05	2.81E-05	2.86E-05	2.59E-05	2.60E-05	2.58E-05
Ps90%/90% (+KTL) Un-Biased	1.63E-03	1.63E-03	1.63E-03	1.63E-03	1.63E-03	1.63E-03	1.63E-03
Ps90%/90% (-KTL) Un-Biased	1.44E-03	1.46E-03	1.47E-03	1.47E-03	1.49E-03	1.49E-03	1.48E-03
Specification MAX	2.80E-03	2.80E-03	2.80E-03	2.80E-03	2.85E-03	2.85E-03	2.85E-03
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

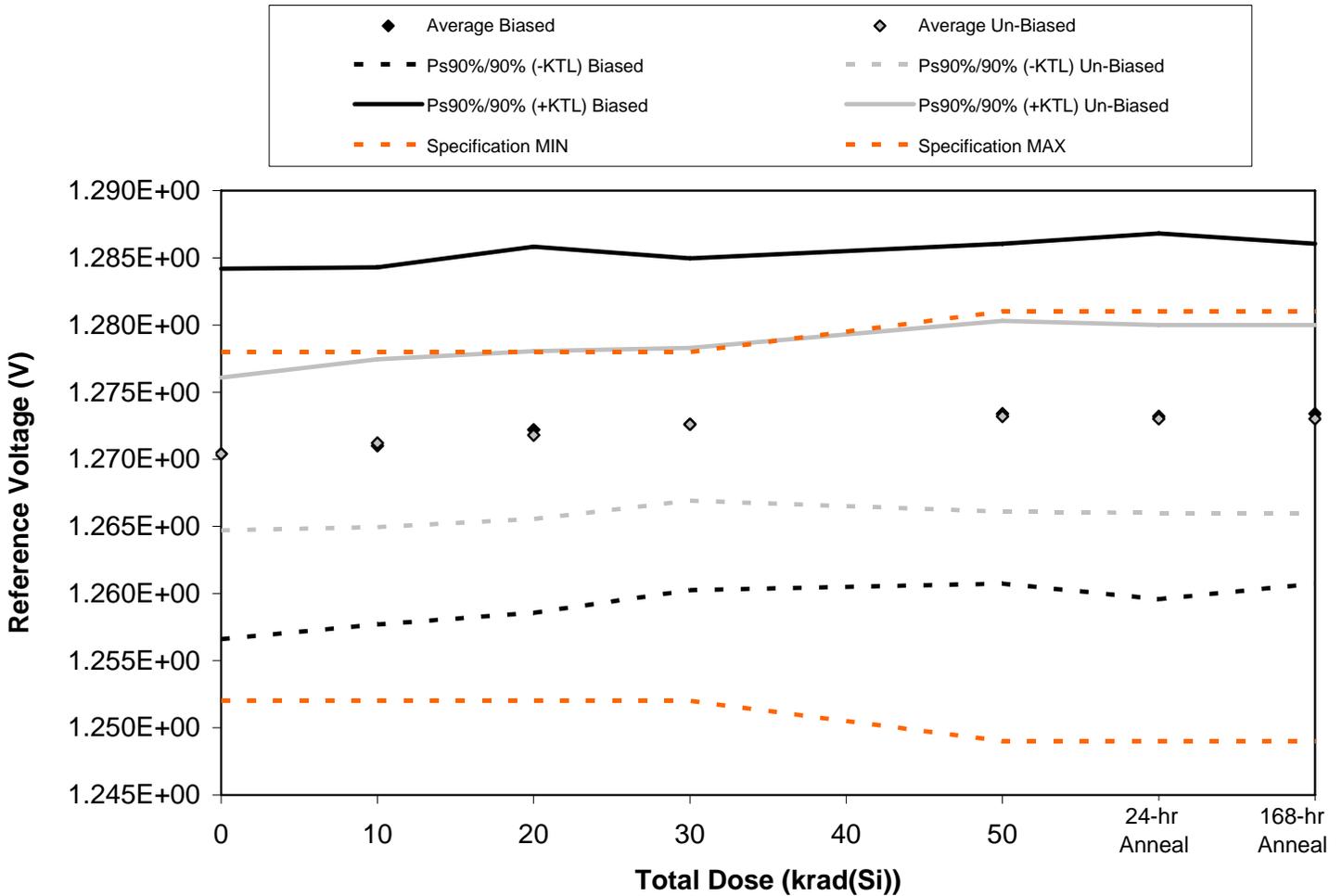


Figure 5.2. Plot of Reference Voltage (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.2. Raw data for Reference Voltage (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

Reference Voltage (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.274	1.275	1.275	1.275	1.276	1.276	1.276
2	1.270	1.271	1.273	1.273	1.274	1.274	1.274
3	1.263	1.264	1.265	1.266	1.267	1.266	1.267
4	1.276	1.276	1.278	1.278	1.279	1.279	1.279
5	1.269	1.269	1.270	1.271	1.271	1.271	1.271
6	1.270	1.271	1.272	1.273	1.274	1.273	1.273
7	1.269	1.269	1.270	1.271	1.271	1.271	1.271
8	1.272	1.273	1.274	1.274	1.275	1.275	1.275
9	1.273	1.274	1.274	1.275	1.276	1.276	1.276
10	1.268	1.269	1.269	1.270	1.270	1.270	1.270
22	1.268	1.269	1.269	1.268	1.268	1.269	1.271
Biased Statistics							
Average Biased	1.270E+00	1.271E+00	1.272E+00	1.273E+00	1.273E+00	1.273E+00	1.273E+00
Std Dev Biased	5.030E-03	4.848E-03	4.970E-03	4.506E-03	4.615E-03	4.970E-03	4.615E-03
Ps90%/90% (+KTL) Biased	1.284E+00	1.284E+00	1.286E+00	1.285E+00	1.286E+00	1.287E+00	1.286E+00
Ps90%/90% (-KTL) Biased	1.257E+00	1.258E+00	1.259E+00	1.260E+00	1.261E+00	1.260E+00	1.261E+00
Un-Biased Statistics							
Average Un-Biased	1.270E+00	1.271E+00	1.272E+00	1.273E+00	1.273E+00	1.273E+00	1.273E+00
Std Dev Un-Biased	2.074E-03	2.280E-03	2.280E-03	2.074E-03	2.588E-03	2.550E-03	2.550E-03
Ps90%/90% (+KTL) Un-Biased	1.276E+00	1.277E+00	1.278E+00	1.278E+00	1.280E+00	1.280E+00	1.280E+00
Ps90%/90% (-KTL) Un-Biased	1.265E+00	1.265E+00	1.266E+00	1.267E+00	1.266E+00	1.266E+00	1.266E+00
Specification MIN	1.252E+00	1.252E+00	1.252E+00	1.252E+00	1.249E+00	1.249E+00	1.249E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	1.278E+00	1.278E+00	1.278E+00	1.278E+00	1.281E+00	1.281E+00	1.281E+00
Status	FAIL	FAIL	FAIL	FAIL	FAIL	FAIL	FAIL

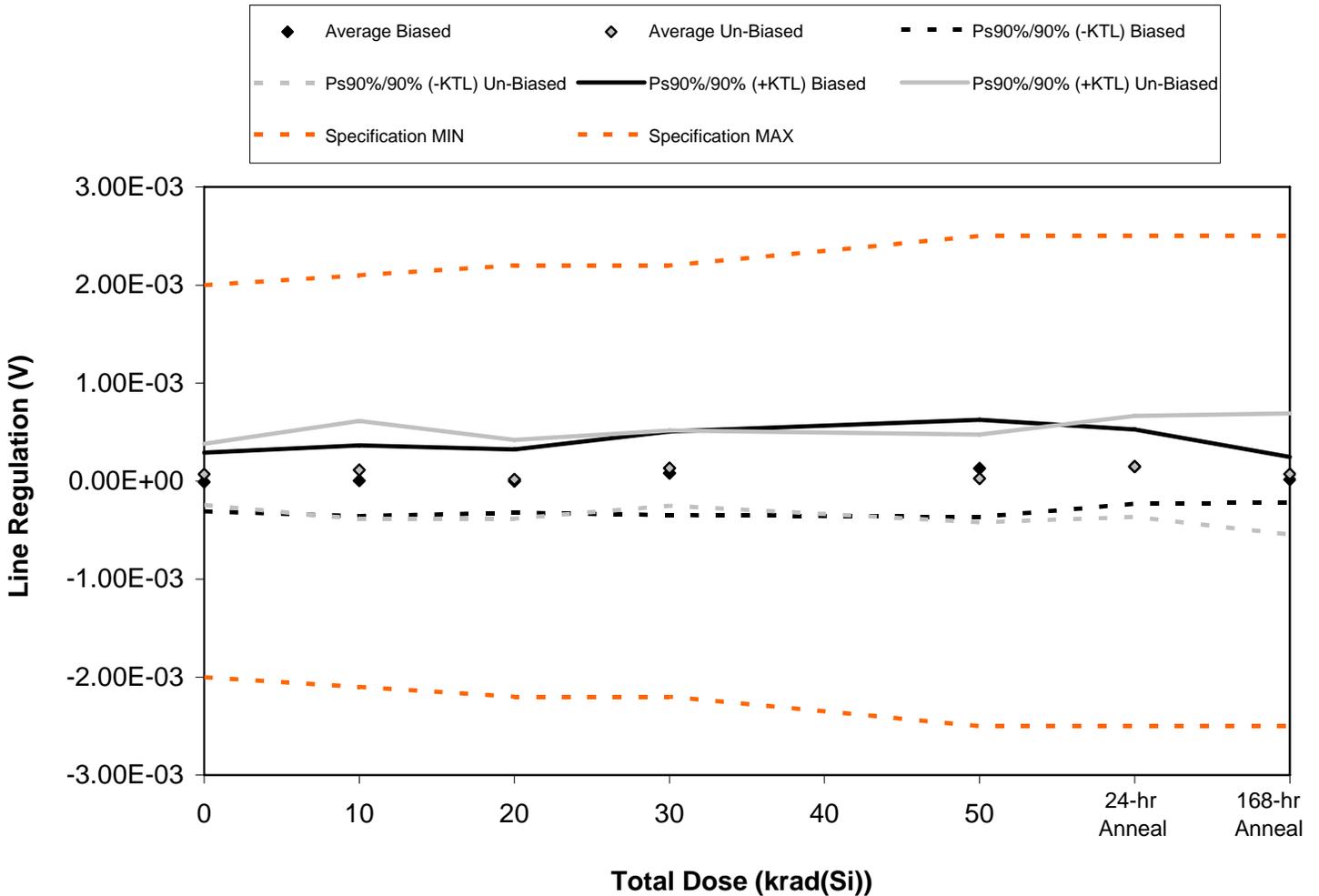


Figure 5.3. Plot of Line Regulation (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.3. Raw data for Line Regulation (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

Line Regulation (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	-9.00E-06	1.61E-04	-1.19E-04	-1.08E-04	3.13E-04	2.36E-04	2.90E-05
2	-2.70E-05	1.31E-04	-3.90E-05	2.40E-04	1.24E-04	2.51E-04	1.05E-04
3	-8.20E-05	-9.20E-05	-8.60E-05	1.87E-04	3.08E-04	1.99E-04	6.30E-05
4	1.72E-04	-7.70E-05	9.00E-05	1.40E-04	-8.30E-05	1.33E-04	-1.18E-04
5	-1.04E-04	-1.07E-04	1.54E-04	-6.20E-05	-1.10E-05	-8.70E-05	1.00E-06
6	-1.00E-04	-2.90E-05	1.94E-04	-8.50E-05	3.12E-04	-1.03E-04	1.30E-05
7	1.73E-04	2.40E-04	-7.50E-05	2.57E-04	-7.70E-05	7.20E-05	2.00E-04
8	1.74E-04	2.20E-04	-9.40E-05	1.41E-04	-7.80E-05	1.19E-04	-1.31E-04
9	3.40E-05	-1.35E-04	1.63E-04	9.40E-05	1.20E-05	3.86E-04	-1.21E-04
10	6.50E-05	2.67E-04	-9.30E-05	2.52E-04	-3.40E-05	2.74E-04	3.96E-04
22	1.78E-04	2.49E-04	1.96E-04	-9.60E-05	3.70E-05	-1.06E-04	9.00E-05
Biased Statistics							
Average Biased	-1.00E-05	3.20E-06	0.00E+00	7.94E-05	1.30E-04	1.46E-04	1.60E-05
Std Dev Biased	1.09E-04	1.31E-04	1.17E-04	1.55E-04	1.81E-04	1.38E-04	8.44E-05
Ps90%/90% (+KTL) Biased	2.89E-04	3.63E-04	3.21E-04	5.05E-04	6.25E-04	5.25E-04	2.47E-04
Ps90%/90% (-KTL) Biased	-3.09E-04	-3.57E-04	-3.21E-04	-3.46E-04	-3.65E-04	-2.33E-04	-2.15E-04
Un-Biased Statistics							
Average Un-Biased	6.92E-05	1.13E-04	1.90E-05	1.32E-04	2.70E-05	1.50E-04	7.14E-05
Std Dev Un-Biased	1.14E-04	1.82E-04	1.46E-04	1.40E-04	1.64E-04	1.88E-04	2.25E-04
Ps90%/90% (+KTL) Un-Biased	3.81E-04	6.13E-04	4.20E-04	5.16E-04	4.75E-04	6.66E-04	6.90E-04
Ps90%/90% (-KTL) Un-Biased	-2.42E-04	-3.87E-04	-3.82E-04	-2.53E-04	-4.21E-04	-3.67E-04	-5.47E-04
Specification MIN	-2.00E-03	-2.10E-03	-2.20E-03	-2.20E-03	-2.50E-03	-2.50E-03	-2.50E-03
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	2.00E-03	2.10E-03	2.20E-03	2.20E-03	2.50E-03	2.50E-03	2.50E-03
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

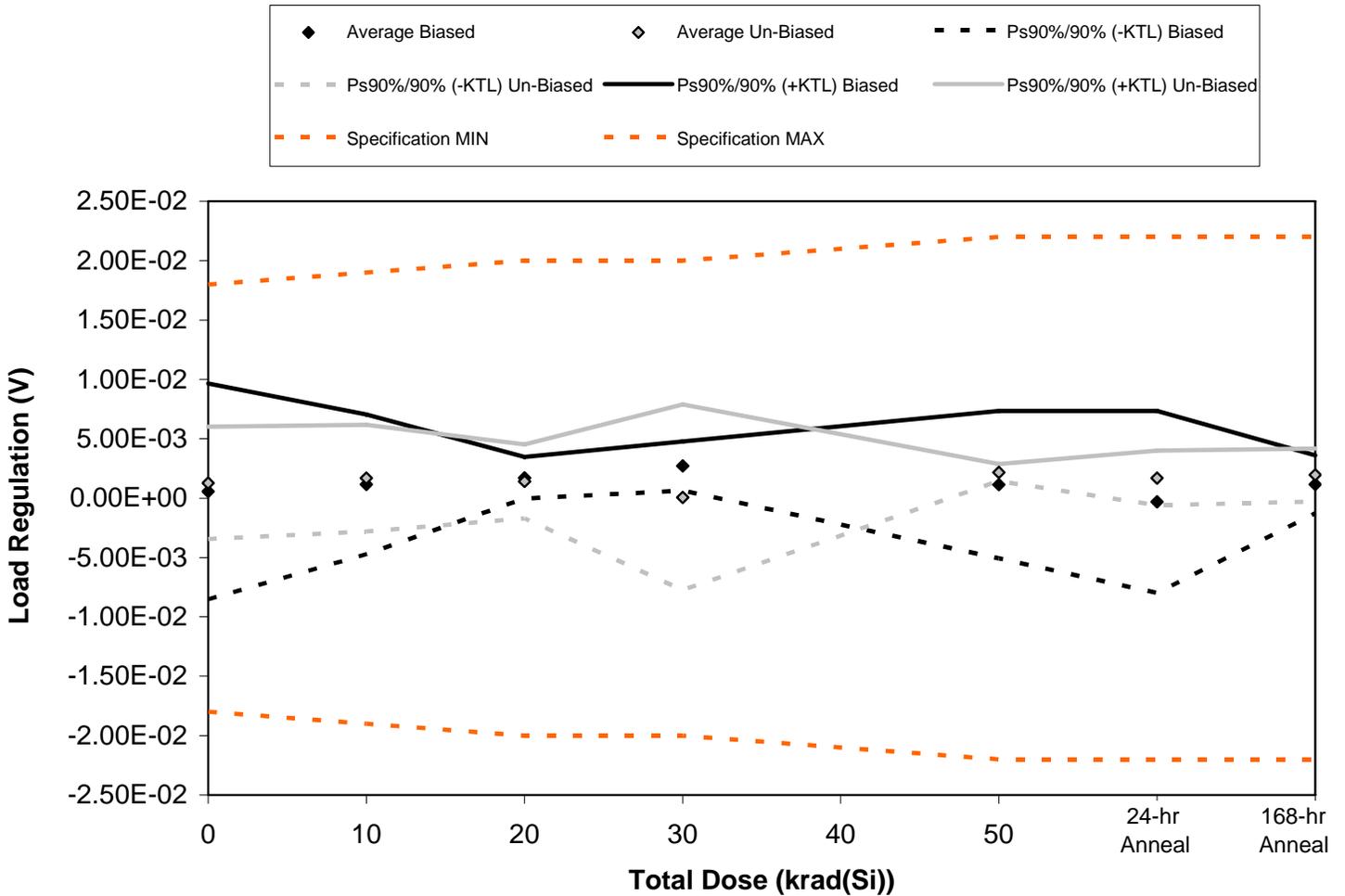


Figure 5.4. Plot of Load Regulation (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.4. Raw data for Load Regulation (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

Load Regulation (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	-5.34E-03	-2.65E-03	1.96E-03	3.71E-03	-2.20E-03	8.10E-05	6.52E-04
2	1.55E-03	2.04E-03	5.70E-04	3.26E-03	8.10E-05	2.00E-03	0.00E+00
3	2.04E-03	2.53E-03	2.04E-03	2.53E-03	2.04E-03	2.53E-03	2.04E-03
4	2.36E-03	1.87E-03	1.96E-03	2.00E-03	3.71E-03	-4.16E-03	1.10E-03
5	2.24E-03	2.04E-03	2.04E-03	2.04E-03	2.04E-03	-2.04E-03	2.04E-03
6	7.33E-04	8.15E-04	4.10E-05	8.15E-04	2.00E-03	2.04E-03	2.04E-03
7	2.44E-04	2.08E-03	3.26E-04	3.26E-04	2.08E-03	1.67E-03	2.04E-03
8	2.20E-03	3.95E-03	2.49E-03	2.04E-03	2.32E-03	2.81E-03	3.06E-03
9	3.79E-03	2.04E-03	2.16E-03	2.00E-03	2.53E-03	5.30E-04	1.83E-03
10	-5.70E-04	-4.48E-04	2.04E-03	-4.86E-03	1.87E-03	1.39E-03	7.74E-04
22	1.87E-03	3.67E-04	-4.08E-03	-1.63E-02	2.77E-03	7.33E-04	-2.04E-02
Biased Statistics							
Average Biased	5.71E-04	1.17E-03	1.71E-03	2.71E-03	1.13E-03	-3.18E-04	1.17E-03
Std Dev Biased	3.32E-03	2.15E-03	6.39E-04	7.57E-04	2.26E-03	2.80E-03	8.87E-04
Ps90%/90% (+KTL) Biased	9.66E-03	7.05E-03	3.46E-03	4.78E-03	7.34E-03	7.35E-03	3.60E-03
Ps90%/90% (-KTL) Biased	-8.52E-03	-4.72E-03	-4.16E-05	6.29E-04	-5.07E-03	-7.99E-03	-1.27E-03
Un-Biased Statistics							
Average Un-Biased	1.28E-03	1.69E-03	1.41E-03	6.28E-05	2.16E-03	1.69E-03	1.95E-03
Std Dev Un-Biased	1.73E-03	1.64E-03	1.14E-03	2.85E-03	2.62E-04	8.39E-04	8.12E-04
Ps90%/90% (+KTL) Un-Biased	6.02E-03	6.18E-03	4.53E-03	7.88E-03	2.88E-03	3.99E-03	4.17E-03
Ps90%/90% (-KTL) Un-Biased	-3.46E-03	-2.80E-03	-1.71E-03	-7.76E-03	1.44E-03	-6.15E-04	-2.78E-04
Specification MIN	-1.80E-02	-1.90E-02	-2.00E-02	-2.00E-02	-2.20E-02	-2.20E-02	-2.20E-02
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	1.80E-02	1.90E-02	2.00E-02	2.00E-02	2.20E-02	2.20E-02	2.20E-02
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

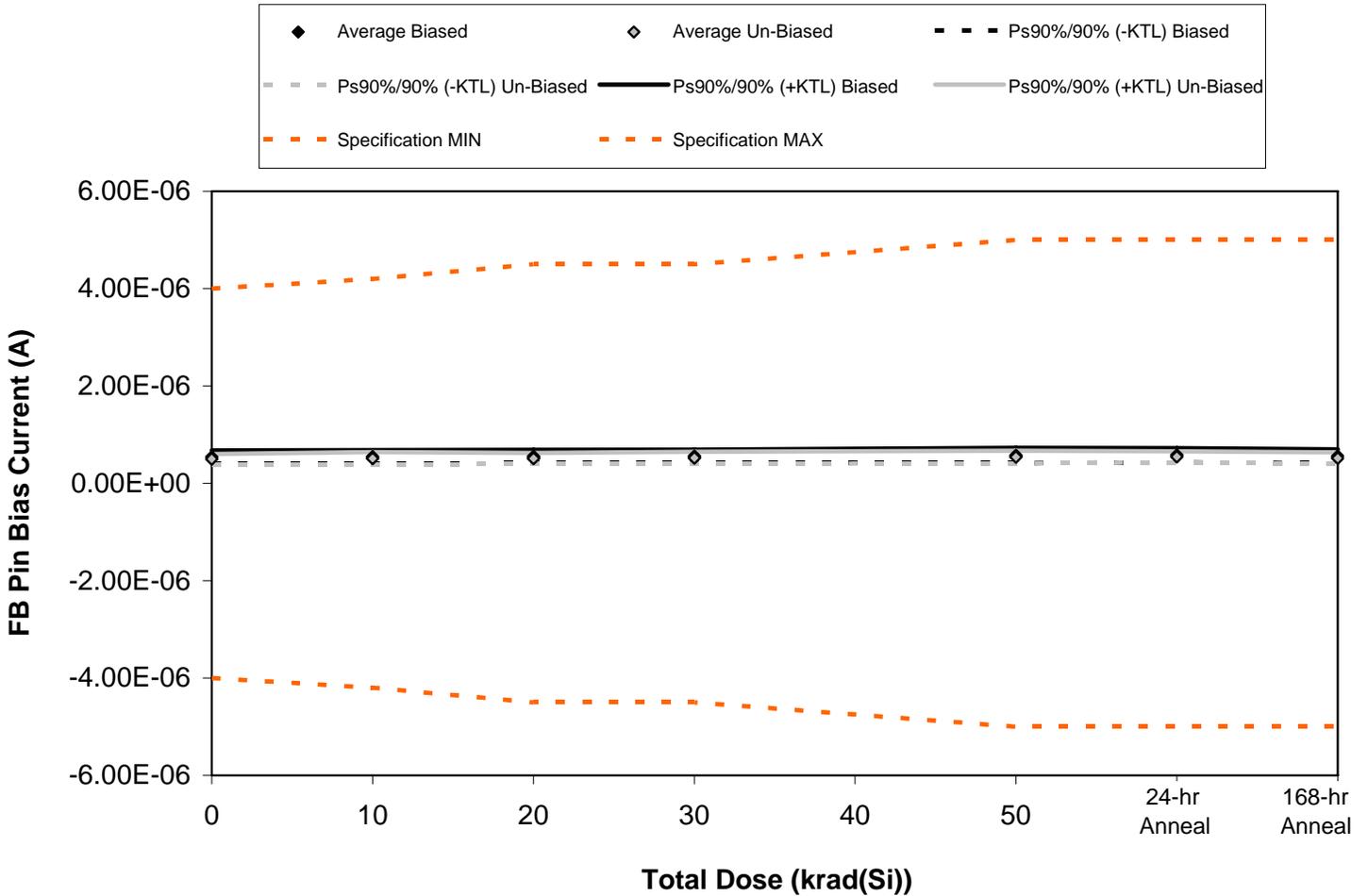


Figure 5.5. Plot of FB Pin Bias Current (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.5. Raw data for FB Pin Bias Current (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

FB Pin Bias Current (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	5.49E-07	5.51E-07	5.70E-07	5.56E-07	5.86E-07	5.89E-07	5.61E-07
2	4.79E-07	4.79E-07	4.89E-07	4.90E-07	4.97E-07	5.16E-07	4.86E-07
3	5.15E-07	5.23E-07	5.24E-07	5.37E-07	5.49E-07	5.45E-07	5.37E-07
4	6.13E-07	6.19E-07	6.22E-07	6.29E-07	6.54E-07	6.57E-07	6.34E-07
5	5.43E-07	5.42E-07	5.52E-07	5.61E-07	5.77E-07	5.79E-07	5.54E-07
6	4.84E-07	4.91E-07	4.98E-07	5.21E-07	5.24E-07	5.33E-07	5.03E-07
7	5.59E-07	5.86E-07	5.80E-07	5.93E-07	6.14E-07	6.12E-07	5.87E-07
8	5.07E-07	5.24E-07	5.23E-07	5.37E-07	5.52E-07	5.49E-07	5.37E-07
9	4.67E-07	4.74E-07	4.82E-07	4.88E-07	5.07E-07	5.16E-07	4.84E-07
10	4.70E-07	4.74E-07	4.84E-07	4.84E-07	4.93E-07	5.09E-07	4.84E-07
22	5.40E-07	5.40E-07	5.42E-07	5.40E-07	5.35E-07	5.40E-07	5.44E-07
Biased Statistics							
Average Biased	5.40E-07	5.43E-07	5.51E-07	5.55E-07	5.73E-07	5.77E-07	5.54E-07
Std Dev Biased	4.94E-08	5.08E-08	4.99E-08	5.02E-08	5.72E-08	5.31E-08	5.33E-08
Ps90%/90% (+KTL) Biased	6.75E-07	6.82E-07	6.88E-07	6.92E-07	7.30E-07	7.23E-07	7.01E-07
Ps90%/90% (-KTL) Biased	4.04E-07	4.03E-07	4.14E-07	4.17E-07	4.16E-07	4.32E-07	4.08E-07
Un-Biased Statistics							
Average Un-Biased	4.97E-07	5.10E-07	5.13E-07	5.25E-07	5.38E-07	5.44E-07	5.19E-07
Std Dev Un-Biased	3.79E-08	4.72E-08	4.07E-08	4.43E-08	4.78E-08	4.12E-08	4.37E-08
Ps90%/90% (+KTL) Un-Biased	6.01E-07	6.39E-07	6.25E-07	6.46E-07	6.69E-07	6.57E-07	6.39E-07
Ps90%/90% (-KTL) Un-Biased	3.94E-07	3.80E-07	4.02E-07	4.03E-07	4.07E-07	4.31E-07	3.99E-07
Specification MIN	-4.00E-06	-4.20E-06	-4.50E-06	-4.50E-06	-5.00E-06	-5.00E-06	-5.00E-06
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	4.00E-06	4.20E-06	4.50E-06	4.50E-06	5.00E-06	5.00E-06	5.00E-06
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

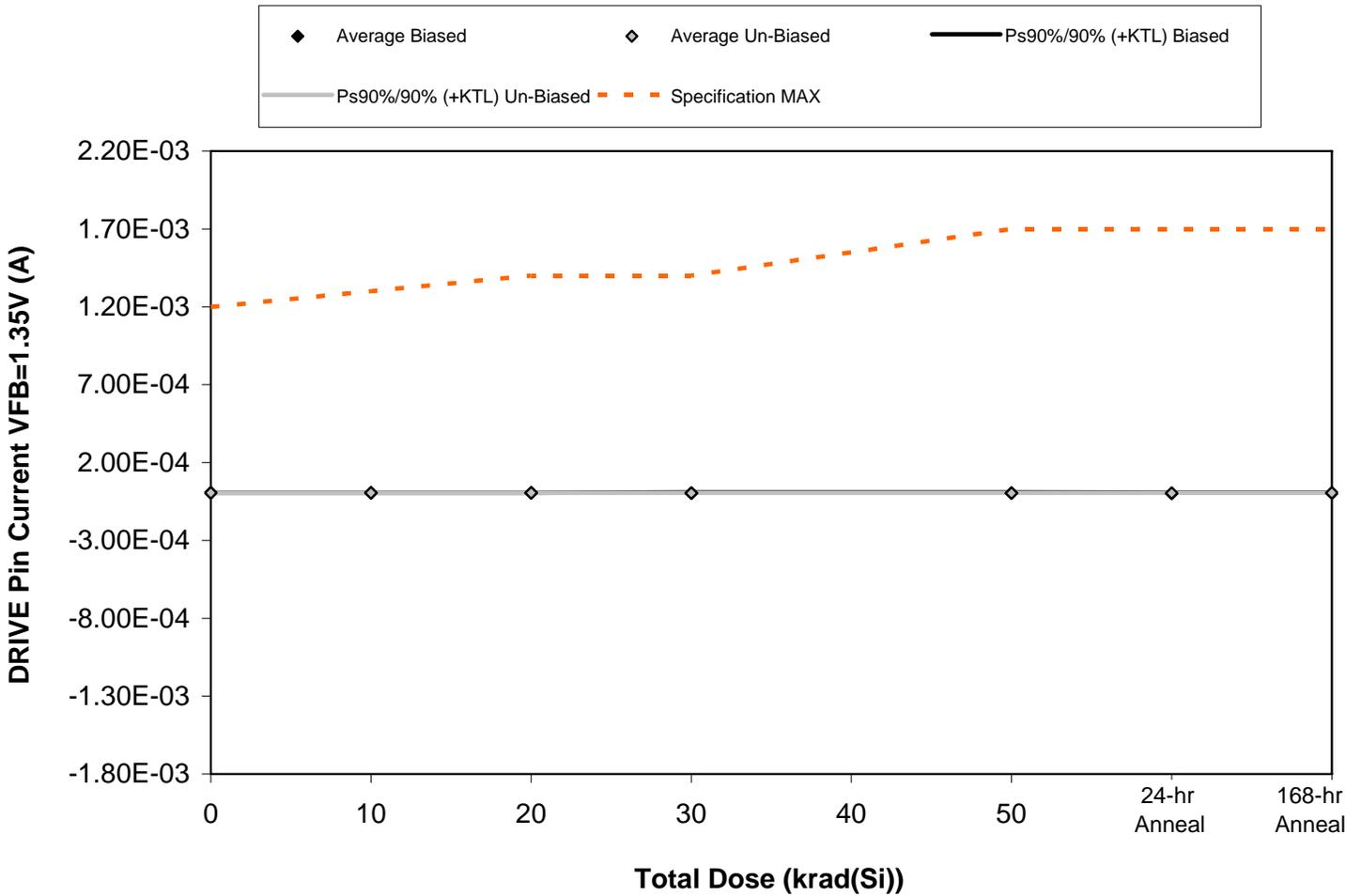


Figure 5.6. Plot of DRIVE Pin Current VFB=1.35V (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.6. Raw data for DRIVE Pin Current VFB=1.35V (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

DRIVE Pin Current VFB=1.35V (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	5.00E-06	5.00E-06	5.00E-06	5.00E-06	5.00E-06	1.00E-06	4.00E-06
2	5.00E-06	5.00E-06	5.00E-06	5.00E-06	1.00E-06	5.00E-06	3.00E-06
3	5.00E-06	5.00E-06	4.00E-06	1.00E-06	3.00E-06	3.00E-06	5.00E-06
4	5.00E-06	5.00E-06	4.00E-06	5.00E-06	4.00E-06	1.00E-06	5.00E-06
5	5.00E-06	5.00E-06	5.00E-06	5.00E-06	5.00E-06	4.00E-06	5.00E-06
6	5.00E-06	5.00E-06	4.00E-06	4.00E-06	5.00E-06	4.00E-06	5.00E-06
7	5.00E-06	5.00E-06	4.00E-06	5.00E-06	3.00E-06	3.00E-06	5.00E-06
8	5.00E-06	5.00E-06	5.00E-06	4.00E-06	3.00E-06	4.00E-06	5.00E-06
9	5.00E-06	5.00E-06	5.00E-06	5.00E-06	4.00E-06	3.00E-06	5.00E-06
10	5.00E-06	5.00E-06	5.00E-06	4.00E-06	3.00E-06	3.00E-06	5.00E-06
22	5.00E-06	5.00E-06	3.00E-06	4.00E-06	3.00E-06	1.00E-06	4.00E-06
Biased Statistics							
Average Biased	5.00E-06	5.00E-06	4.60E-06	4.20E-06	3.60E-06	2.80E-06	4.40E-06
Std Dev Biased	0.00E+00	0.00E+00	5.48E-07	1.79E-06	1.67E-06	1.79E-06	8.94E-07
Ps90%/90% (+KTL) Biased	5.00E-06	5.00E-06	6.10E-06	9.11E-06	8.19E-06	7.71E-06	6.85E-06
Ps90%/90% (-KTL) Biased	5.00E-06	5.00E-06	3.10E-06	-7.05E-07	-9.88E-07	-2.11E-06	1.95E-06
Un-Biased Statistics							
Average Un-Biased	5.00E-06	5.00E-06	4.60E-06	4.40E-06	3.60E-06	3.40E-06	5.00E-06
Std Dev Un-Biased	0.00E+00	0.00E+00	5.48E-07	5.48E-07	8.94E-07	5.48E-07	0.00E+00
Ps90%/90% (+KTL) Un-Biased	5.00E-06	5.00E-06	6.10E-06	5.90E-06	6.05E-06	4.90E-06	5.00E-06
Ps90%/90% (-KTL) Un-Biased	5.00E-06	5.00E-06	3.10E-06	2.90E-06	1.15E-06	1.90E-06	5.00E-06
Specification MAX	1.20E-03	1.30E-03	1.40E-03	1.40E-03	1.70E-03	1.70E-03	1.70E-03
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

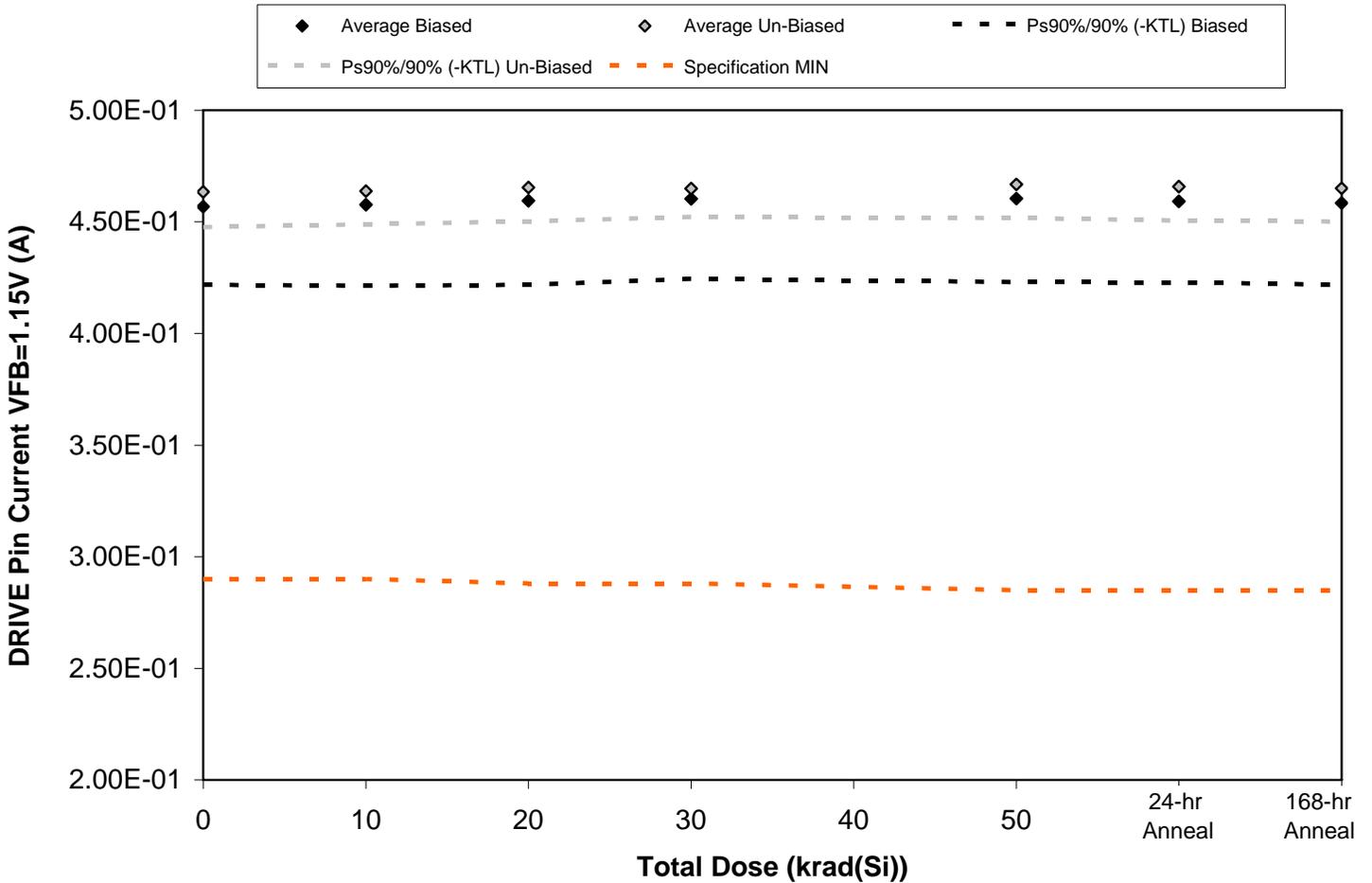


Figure 5.7. Plot of DRIVE Pin Current VFB=1.15V (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.7. Raw data for DRIVE Pin Current VFB=1.15V (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

DRIVE Pin Current VFB=1.15V (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	4.53E-01	4.53E-01	4.52E-01	4.56E-01	4.55E-01	4.54E-01	4.53E-01
2	4.65E-01	4.66E-01	4.69E-01	4.69E-01	4.69E-01	4.68E-01	4.67E-01
3	4.70E-01	4.73E-01	4.75E-01	4.75E-01	4.76E-01	4.74E-01	4.73E-01
4	4.37E-01	4.38E-01	4.40E-01	4.41E-01	4.40E-01	4.39E-01	4.39E-01
5	4.59E-01	4.59E-01	4.62E-01	4.62E-01	4.62E-01	4.61E-01	4.60E-01
6	4.69E-01	4.70E-01	4.72E-01	4.69E-01	4.73E-01	4.72E-01	4.71E-01
7	4.56E-01	4.56E-01	4.58E-01	4.59E-01	4.60E-01	4.58E-01	4.58E-01
8	4.67E-01	4.67E-01	4.69E-01	4.68E-01	4.70E-01	4.69E-01	4.68E-01
9	4.59E-01	4.60E-01	4.61E-01	4.61E-01	4.63E-01	4.62E-01	4.61E-01
10	4.66E-01	4.66E-01	4.68E-01	4.68E-01	4.69E-01	4.68E-01	4.67E-01
22	4.51E-01	4.50E-01	4.52E-01	4.52E-01	4.52E-01	4.51E-01	4.51E-01
Biased Statistics							
Average Biased	4.57E-01	4.58E-01	4.59E-01	4.60E-01	4.60E-01	4.59E-01	4.58E-01
Std Dev Biased	1.28E-02	1.32E-02	1.38E-02	1.31E-02	1.36E-02	1.33E-02	1.34E-02
Ps90%/90% (+KTL) Biased	4.92E-01	4.94E-01	4.97E-01	4.96E-01	4.98E-01	4.96E-01	4.95E-01
Ps90%/90% (-KTL) Biased	4.22E-01	4.21E-01	4.22E-01	4.25E-01	4.23E-01	4.23E-01	4.22E-01
Un-Biased Statistics							
Average Un-Biased	4.63E-01	4.64E-01	4.65E-01	4.65E-01	4.67E-01	4.66E-01	4.65E-01
Std Dev Un-Biased	5.72E-03	5.47E-03	5.56E-03	4.65E-03	5.50E-03	5.51E-03	5.46E-03
Ps90%/90% (+KTL) Un-Biased	4.79E-01	4.79E-01	4.81E-01	4.78E-01	4.82E-01	4.81E-01	4.80E-01
Ps90%/90% (-KTL) Un-Biased	4.48E-01	4.49E-01	4.50E-01	4.52E-01	4.52E-01	4.51E-01	4.50E-01
Specification MIN	2.90E-01	2.90E-01	2.88E-01	2.88E-01	2.85E-01	2.85E-01	2.85E-01
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

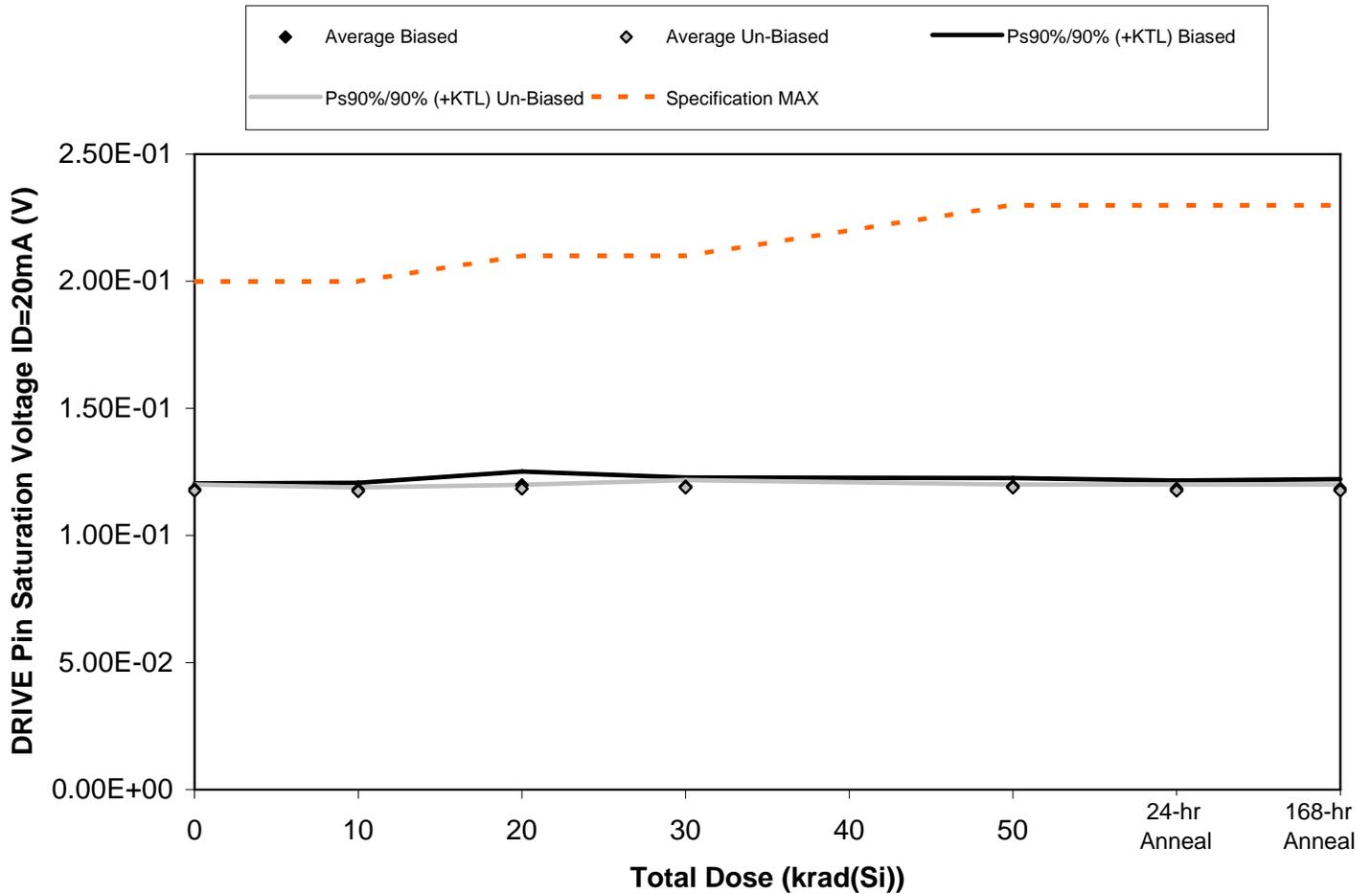


Figure 5.8. Plot of DRIVE Pin Saturation Voltage ID=20mA (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.8. Raw data for DRIVE Pin Saturation Voltage ID=20mA (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

DRIVE Pin Saturation Voltage ID=20mA (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.19E-01	1.19E-01	1.23E-01	1.20E-01	1.21E-01	1.19E-01	1.19E-01
2	1.18E-01	1.17E-01	1.19E-01	1.18E-01	1.19E-01	1.18E-01	1.19E-01
3	1.18E-01	1.17E-01	1.18E-01	1.18E-01	1.18E-01	1.17E-01	1.17E-01
4	1.19E-01	1.19E-01	1.20E-01	1.21E-01	1.20E-01	1.20E-01	1.20E-01
5	1.17E-01	1.18E-01	1.19E-01	1.19E-01	1.19E-01	1.18E-01	1.17E-01
6	1.17E-01	1.17E-01	1.18E-01	1.20E-01	1.19E-01	1.17E-01	1.17E-01
7	1.17E-01	1.17E-01	1.18E-01	1.19E-01	1.19E-01	1.17E-01	1.17E-01
8	1.17E-01	1.17E-01	1.18E-01	1.17E-01	1.18E-01	1.17E-01	1.17E-01
9	1.19E-01	1.18E-01	1.19E-01	1.19E-01	1.19E-01	1.19E-01	1.19E-01
10	1.18E-01	1.18E-01	1.19E-01	1.19E-01	1.19E-01	1.18E-01	1.18E-01
22	1.18E-01	1.18E-01	1.19E-01	1.20E-01	1.19E-01	1.19E-01	1.20E-01
Biased Statistics							
Average Biased	1.18E-01	1.18E-01	1.20E-01	1.19E-01	1.19E-01	1.18E-01	1.18E-01
Std Dev Biased	8.37E-04	1.00E-03	1.92E-03	1.30E-03	1.14E-03	1.14E-03	1.34E-03
Ps90%/90% (+KTL) Biased	1.20E-01	1.21E-01	1.25E-01	1.23E-01	1.23E-01	1.22E-01	1.22E-01
Ps90%/90% (-KTL) Biased	1.16E-01	1.15E-01	1.15E-01	1.16E-01	1.16E-01	1.15E-01	1.15E-01
Un-Biased Statistics							
Average Un-Biased	1.18E-01	1.17E-01	1.18E-01	1.19E-01	1.19E-01	1.18E-01	1.18E-01
Std Dev Un-Biased	8.94E-04	5.48E-04	5.48E-04	1.10E-03	4.47E-04	8.94E-04	8.94E-04
Ps90%/90% (+KTL) Un-Biased	1.20E-01	1.19E-01	1.20E-01	1.22E-01	1.20E-01	1.20E-01	1.20E-01
Ps90%/90% (-KTL) Un-Biased	1.15E-01	1.16E-01	1.17E-01	1.16E-01	1.18E-01	1.15E-01	1.15E-01
Specification MAX	2.00E-01	2.00E-01	2.10E-01	2.10E-01	2.30E-01	2.30E-01	2.30E-01
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

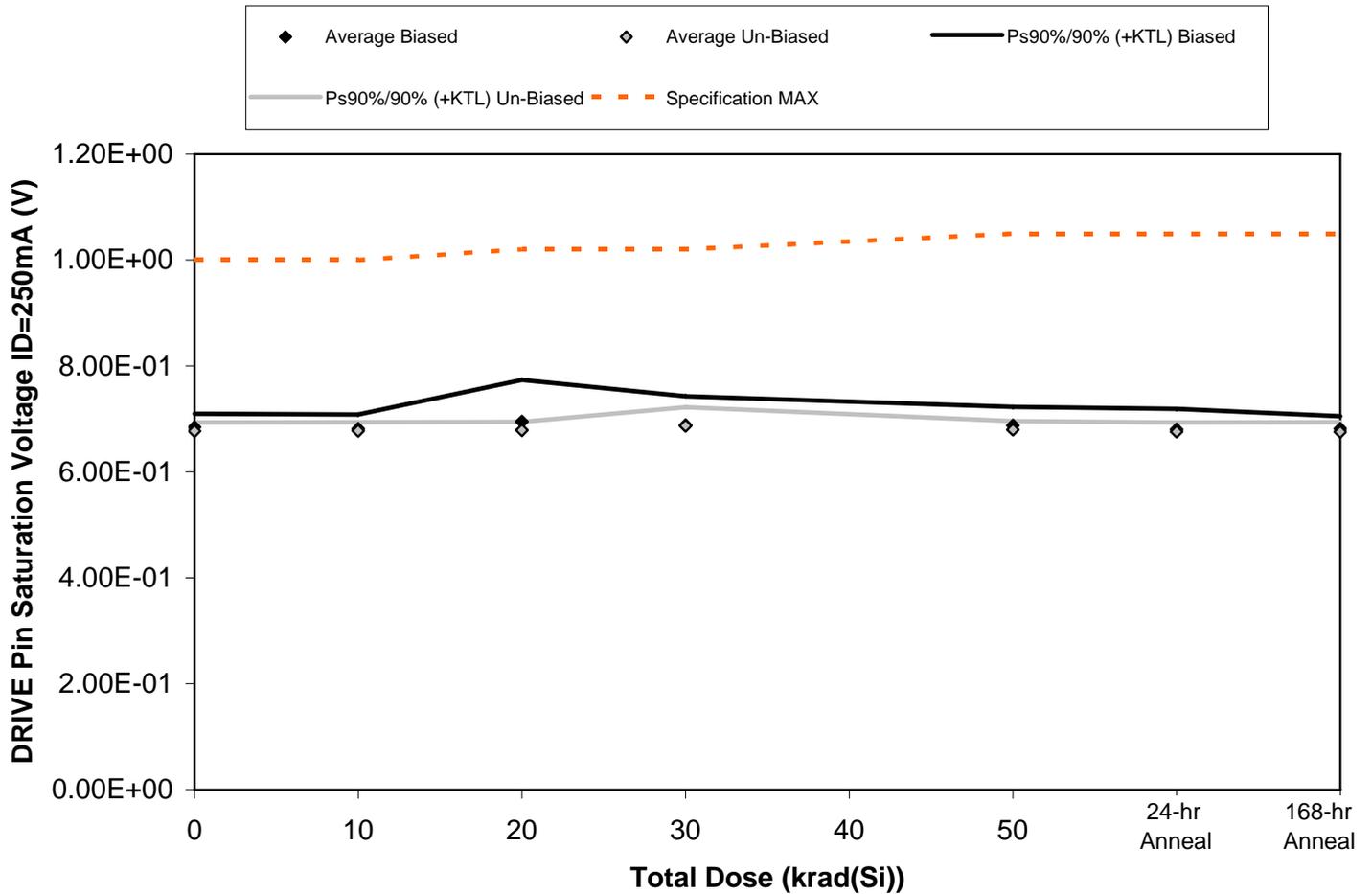


Figure 5.9. Plot of DRIVE Pin Saturation Voltage ID=250mA (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.9. Raw data for DRIVE Pin Saturation Voltage ID=250mA (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

DRIVE Pin Saturation Voltage ID=250mA (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	6.94E-01	6.92E-01	7.44E-01	7.03E-01	7.06E-01	6.82E-01	6.85E-01
2	6.72E-01	6.77E-01	6.77E-01	6.69E-01	6.78E-01	6.69E-01	6.80E-01
3	6.86E-01	6.67E-01	6.74E-01	6.69E-01	6.76E-01	6.65E-01	6.68E-01
4	6.92E-01	6.88E-01	6.95E-01	7.13E-01	6.95E-01	7.01E-01	6.92E-01
5	6.78E-01	6.83E-01	6.85E-01	6.87E-01	6.83E-01	6.83E-01	6.80E-01
6	6.74E-01	6.77E-01	6.78E-01	7.04E-01	6.81E-01	6.69E-01	6.69E-01
7	6.85E-01	6.80E-01	6.83E-01	6.92E-01	6.83E-01	6.81E-01	6.82E-01
8	6.69E-01	6.67E-01	6.69E-01	6.69E-01	6.69E-01	6.69E-01	6.69E-01
9	6.80E-01	6.82E-01	6.83E-01	6.83E-01	6.83E-01	6.83E-01	6.83E-01
10	6.77E-01	6.81E-01	6.80E-01	6.87E-01	6.82E-01	6.76E-01	6.74E-01
22	6.81E-01	6.80E-01	6.89E-01	7.00E-01	6.83E-01	6.83E-01	7.06E-01
Biased Statistics							
Average Biased	6.84E-01	6.81E-01	6.95E-01	6.88E-01	6.88E-01	6.80E-01	6.81E-01
Std Dev Biased	9.32E-03	9.81E-03	2.86E-02	1.98E-02	1.27E-02	1.41E-02	8.77E-03
Ps90%/90% (+KTL) Biased	7.10E-01	7.08E-01	7.73E-01	7.43E-01	7.22E-01	7.19E-01	7.05E-01
Ps90%/90% (-KTL) Biased	6.59E-01	6.54E-01	6.17E-01	6.34E-01	6.53E-01	6.41E-01	6.57E-01
Un-Biased Statistics							
Average Un-Biased	6.77E-01	6.77E-01	6.79E-01	6.87E-01	6.80E-01	6.76E-01	6.75E-01
Std Dev Un-Biased	6.04E-03	6.11E-03	5.77E-03	1.28E-02	5.98E-03	6.54E-03	6.80E-03
Ps90%/90% (+KTL) Un-Biased	6.94E-01	6.94E-01	6.94E-01	7.22E-01	6.96E-01	6.94E-01	6.94E-01
Ps90%/90% (-KTL) Un-Biased	6.60E-01	6.61E-01	6.63E-01	6.52E-01	6.63E-01	6.58E-01	6.57E-01
Specification MAX	1.00E+00	1.00E+00	1.02E+00	1.02E+00	1.05E+00	1.05E+00	1.05E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

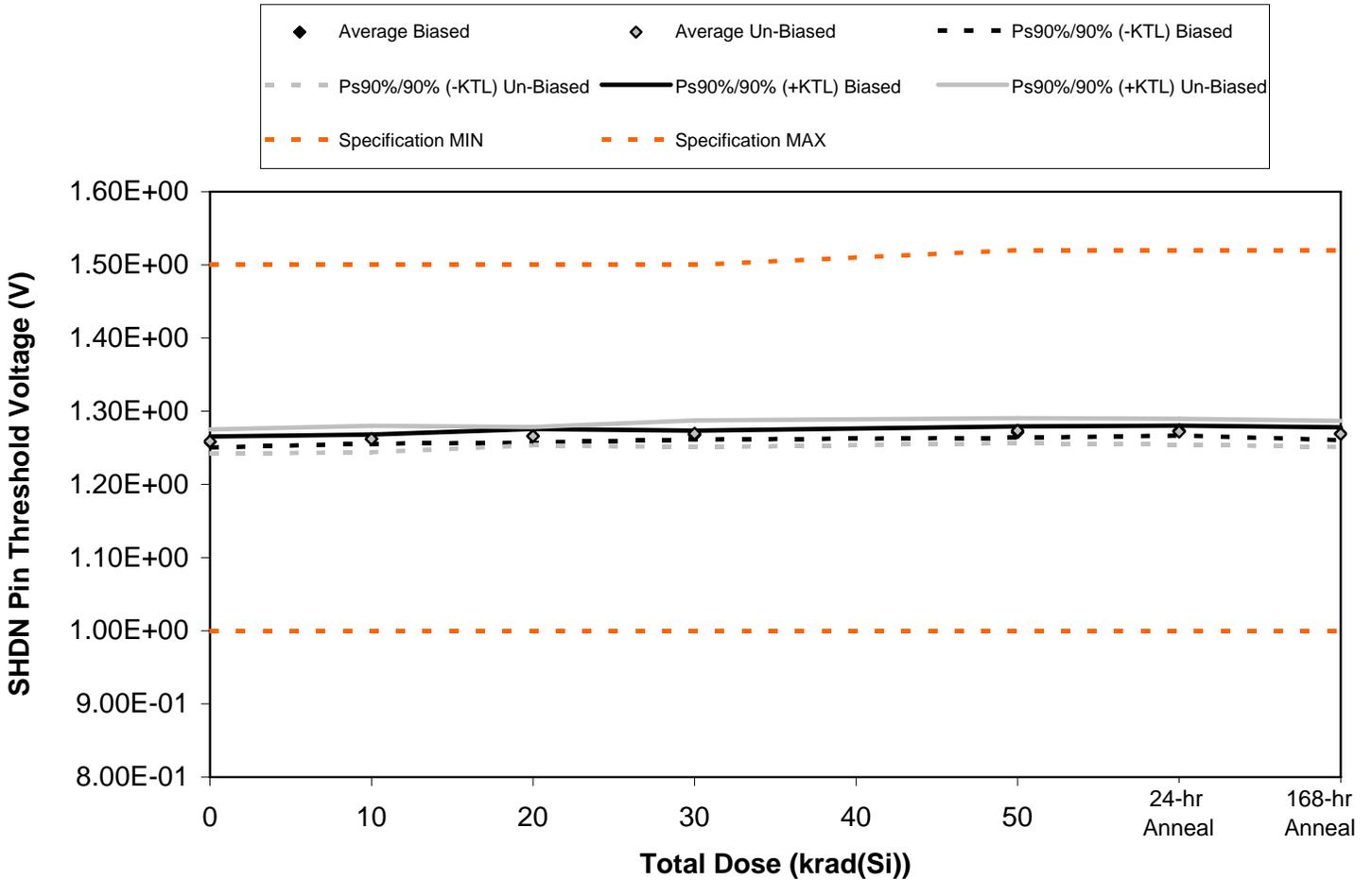


Figure 5.10. Plot of SHDN Pin Threshold Voltage (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.10. Raw data for SHDN Pin Threshold Voltage (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

SHDN Pin Threshold Voltage (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.28E+00	1.27E+00
2	1.26E+00	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00
3	1.26E+00	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00
4	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00
5	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.28E+00	1.28E+00	1.27E+00
6	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.28E+00	1.27E+00	1.27E+00
7	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.28E+00	1.28E+00	1.27E+00
8	1.25E+00	1.26E+00	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.26E+00
9	1.27E+00	1.27E+00	1.27E+00	1.28E+00	1.28E+00	1.28E+00	1.28E+00
10	1.25E+00	1.26E+00	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.26E+00
22	1.26E+00	1.26E+00	1.26E+00	1.25E+00	1.26E+00	1.26E+00	1.25E+00
Biased Statistics							
Average Biased	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00
Std Dev Biased	2.74E-03	2.24E-03	3.42E-03	2.19E-03	2.88E-03	2.51E-03	3.21E-03
Ps90%/90% (+KTL) Biased	1.27E+00	1.27E+00	1.28E+00	1.27E+00	1.28E+00	1.28E+00	1.28E+00
Ps90%/90% (-KTL) Biased	1.25E+00	1.26E+00	1.26E+00	1.26E+00	1.26E+00	1.27E+00	1.26E+00
Un-Biased Statistics							
Average Un-Biased	1.26E+00	1.26E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00	1.27E+00
Std Dev Un-Biased	5.98E-03	6.52E-03	4.55E-03	6.72E-03	6.23E-03	6.52E-03	6.50E-03
Ps90%/90% (+KTL) Un-Biased	1.28E+00	1.28E+00	1.28E+00	1.29E+00	1.29E+00	1.29E+00	1.29E+00
Ps90%/90% (-KTL) Un-Biased	1.24E+00	1.24E+00	1.25E+00	1.25E+00	1.26E+00	1.25E+00	1.25E+00
Specification MIN	1.00E+00	1.00E+00	1.00E+00	1.00E+00	1.00E+00	1.00E+00	1.00E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	1.50E+00	1.50E+00	1.50E+00	1.50E+00	1.52E+00	1.52E+00	1.52E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

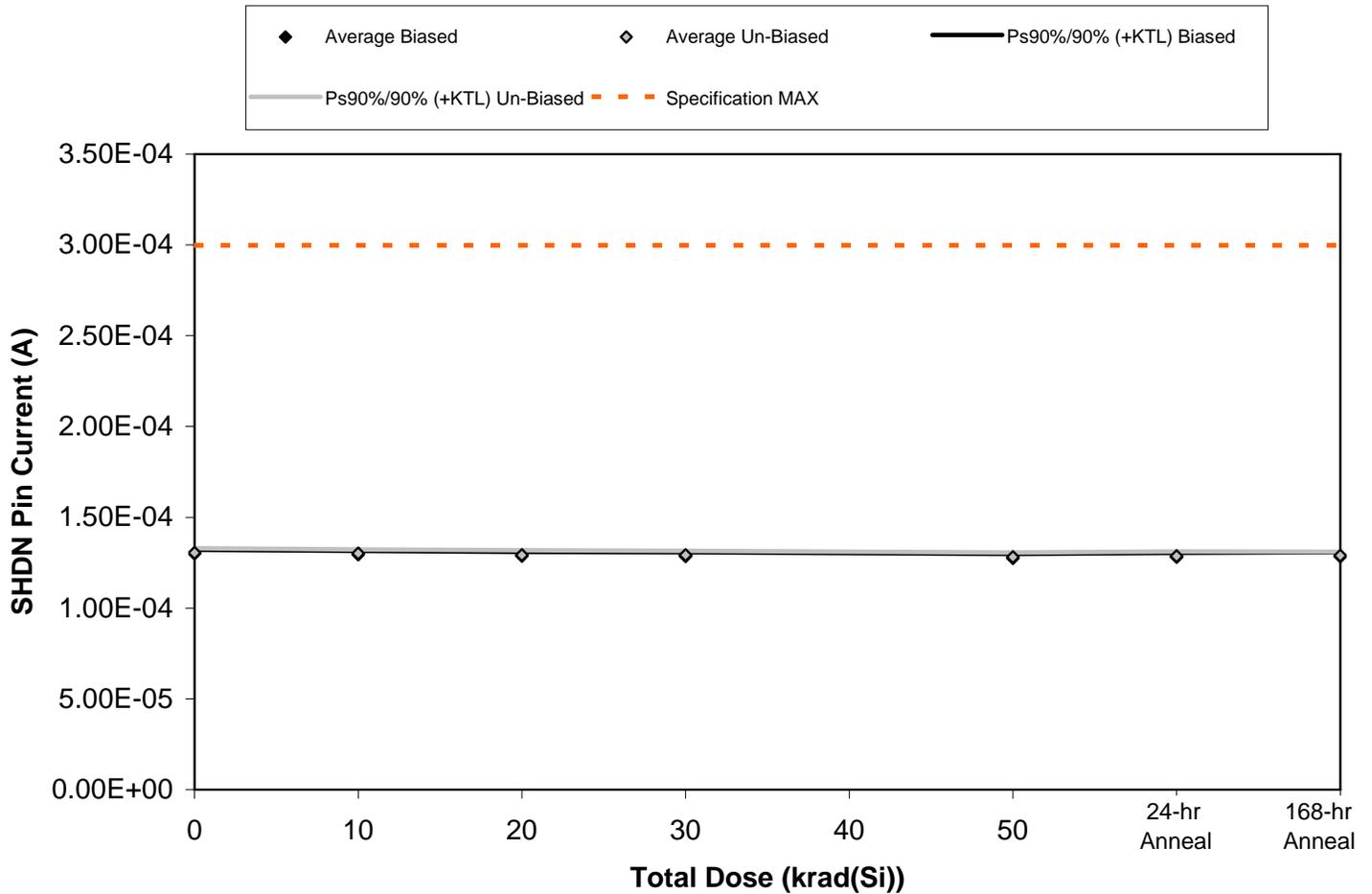


Figure 5.11. Plot of SHDN Pin Current (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.11. Raw data for SHDN Pin Current (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

SHDN Pin Current (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.29E-04	1.29E-04	1.28E-04	1.28E-04	1.27E-04	1.27E-04	1.28E-04
2	1.30E-04	1.29E-04	1.28E-04	1.28E-04	1.27E-04	1.28E-04	1.28E-04
3	1.31E-04	1.30E-04	1.29E-04	1.29E-04	1.28E-04	1.29E-04	1.30E-04
4	1.31E-04	1.30E-04	1.30E-04	1.29E-04	1.28E-04	1.29E-04	1.29E-04
5	1.29E-04	1.29E-04	1.28E-04	1.28E-04	1.27E-04	1.27E-04	1.28E-04
6	1.30E-04	1.30E-04	1.29E-04	1.29E-04	1.28E-04	1.28E-04	1.29E-04
7	1.32E-04	1.31E-04	1.31E-04	1.31E-04	1.30E-04	1.30E-04	1.30E-04
8	1.31E-04	1.30E-04	1.29E-04	1.29E-04	1.28E-04	1.29E-04	1.29E-04
9	1.30E-04	1.30E-04	1.28E-04	1.29E-04	1.27E-04	1.28E-04	1.28E-04
10	1.30E-04	1.29E-04	1.29E-04	1.29E-04	1.27E-04	1.28E-04	1.28E-04
22	1.29E-04	1.30E-04	1.29E-04	1.30E-04	1.29E-04	1.29E-04	1.30E-04
Biased Statistics							
Average Biased	1.30E-04	1.30E-04	1.29E-04	1.29E-04	1.27E-04	1.28E-04	1.28E-04
Std Dev Biased	8.04E-07	7.37E-07	7.89E-07	8.03E-07	8.76E-07	8.45E-07	7.97E-07
Ps90%/90% (+KTL) Biased	1.32E-04	1.32E-04	1.31E-04	1.31E-04	1.30E-04	1.30E-04	1.31E-04
Ps90%/90% (-KTL) Biased	1.28E-04	1.28E-04	1.27E-04	1.26E-04	1.25E-04	1.26E-04	1.26E-04
Un-Biased Statistics							
Average Un-Biased	1.30E-04	1.30E-04	1.29E-04	1.29E-04	1.28E-04	1.29E-04	1.29E-04
Std Dev Un-Biased	9.12E-07	8.04E-07	9.49E-07	8.36E-07	9.41E-07	9.35E-07	7.57E-07
Ps90%/90% (+KTL) Un-Biased	1.33E-04	1.32E-04	1.32E-04	1.32E-04	1.31E-04	1.31E-04	1.31E-04
Ps90%/90% (-KTL) Un-Biased	1.28E-04	1.28E-04	1.27E-04	1.27E-04	1.25E-04	1.26E-04	1.27E-04
Specification MAX	3.00E-04	3.00E-04	3.00E-04	3.00E-04	3.00E-04	3.00E-04	3.00E-04
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

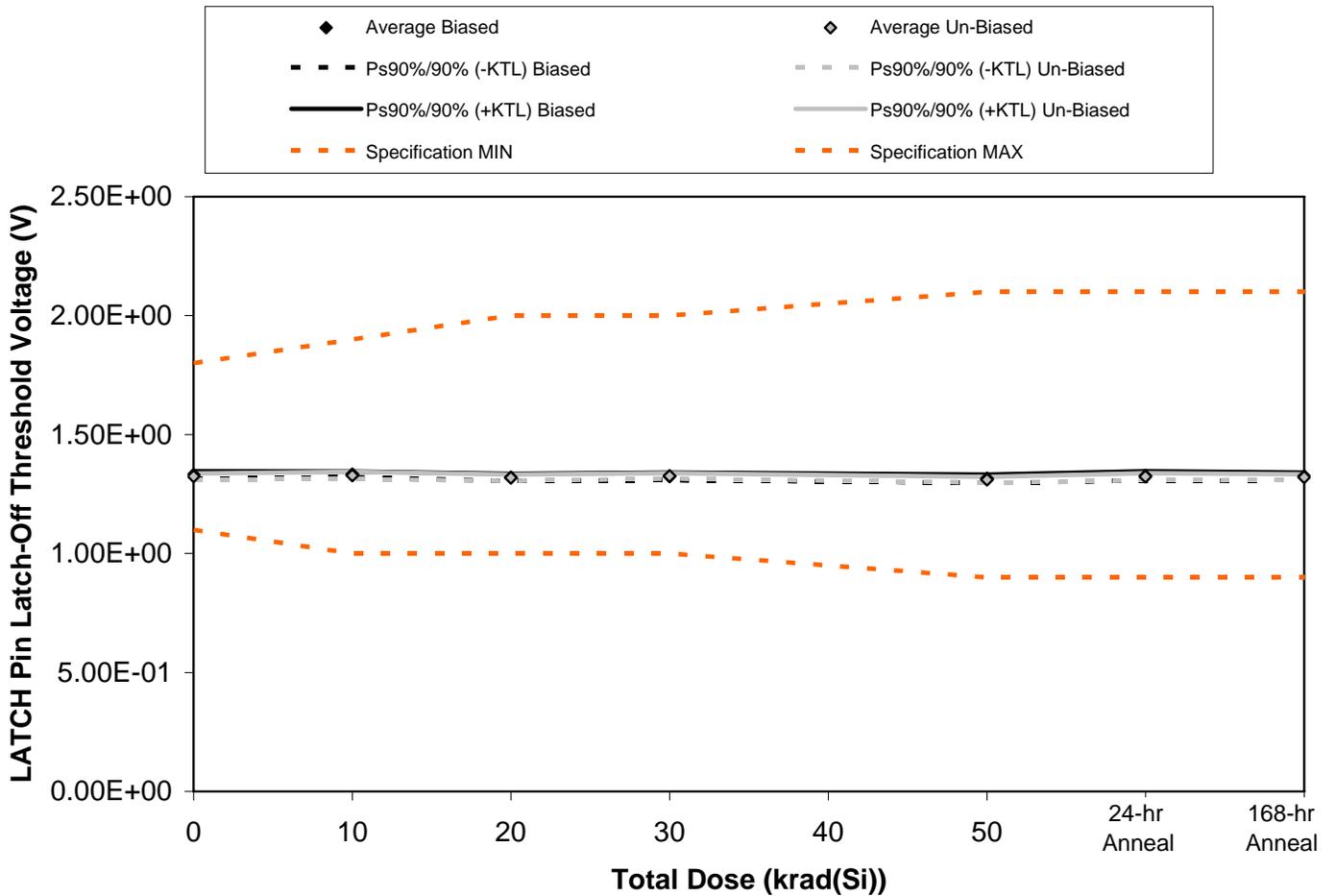


Figure 5.12. Plot of LATCH Pin Latch-Off Threshold Voltage (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.12. Raw data for LATCH Pin Latch-Off Threshold Voltage (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

LATCH Pin Latch-Off Threshold Voltage (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.33E+00	1.34E+00	1.33E+00	1.32E+00	1.32E+00	1.33E+00	1.32E+00
2	1.32E+00	1.33E+00	1.31E+00	1.32E+00	1.31E+00	1.32E+00	1.32E+00
3	1.33E+00	1.33E+00	1.32E+00	1.32E+00	1.31E+00	1.32E+00	1.32E+00
4	1.34E+00	1.34E+00	1.32E+00	1.33E+00	1.32E+00	1.34E+00	1.33E+00
5	1.33E+00	1.33E+00	1.32E+00	1.33E+00	1.32E+00	1.33E+00	1.33E+00
6	1.32E+00	1.33E+00	1.32E+00	1.32E+00	1.31E+00	1.32E+00	1.32E+00
7	1.33E+00	1.34E+00	1.33E+00	1.33E+00	1.32E+00	1.33E+00	1.33E+00
8	1.32E+00	1.33E+00	1.32E+00	1.33E+00	1.31E+00	1.32E+00	1.32E+00
9	1.32E+00	1.33E+00	1.32E+00	1.33E+00	1.31E+00	1.32E+00	1.32E+00
10	1.32E+00	1.32E+00	1.32E+00	1.32E+00	1.31E+00	1.32E+00	1.32E+00
22	1.33E+00	1.33E+00	1.33E+00	1.33E+00	1.32E+00	1.33E+00	1.33E+00
Biased Statistics							
Average Biased	1.33E+00	1.33E+00	1.32E+00	1.32E+00	1.31E+00	1.33E+00	1.32E+00
Std Dev Biased	5.70E-03	4.18E-03	5.70E-03	5.70E-03	6.43E-03	7.42E-03	5.70E-03
Ps90%/90% (+KTL) Biased	1.35E+00	1.34E+00	1.34E+00	1.34E+00	1.33E+00	1.35E+00	1.34E+00
Ps90%/90% (-KTL) Biased	1.31E+00	1.32E+00	1.30E+00	1.31E+00	1.30E+00	1.31E+00	1.31E+00
Un-Biased Statistics							
Average Un-Biased	1.32E+00	1.33E+00	1.32E+00	1.33E+00	1.31E+00	1.32E+00	1.32E+00
Std Dev Un-Biased	4.47E-03	5.48E-03	4.77E-03	4.18E-03	4.32E-03	5.48E-03	4.18E-03
Ps90%/90% (+KTL) Un-Biased	1.34E+00	1.34E+00	1.33E+00	1.34E+00	1.32E+00	1.34E+00	1.33E+00
Ps90%/90% (-KTL) Un-Biased	1.31E+00	1.31E+00	1.31E+00	1.31E+00	1.30E+00	1.31E+00	1.31E+00
Specification MIN	1.10E+00	1.00E+00	1.00E+00	1.00E+00	9.00E-01	9.00E-01	9.00E-01
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	1.80E+00	1.90E+00	2.00E+00	2.00E+00	2.10E+00	2.10E+00	2.10E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

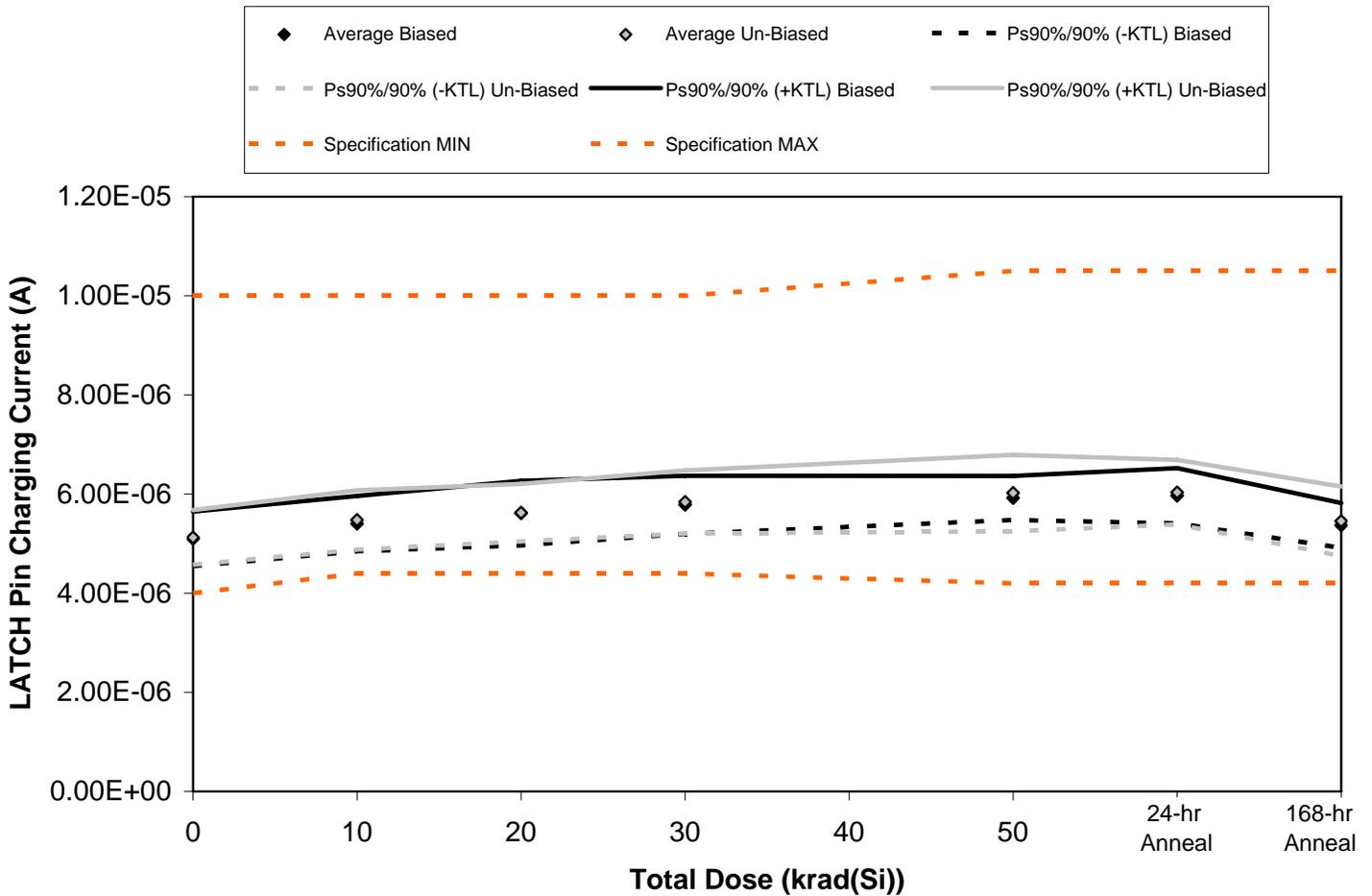


Figure 5.13. Plot of LATCH Pin Charging Current (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.13. Raw data for LATCH Pin Charging Current (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

LATCH Pin Charging Current (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	5.18E-06	5.49E-06	5.92E-06	5.86E-06	5.94E-06	5.98E-06	5.38E-06
2	4.88E-06	5.19E-06	5.37E-06	5.56E-06	5.74E-06	5.76E-06	5.21E-06
3	4.99E-06	5.29E-06	5.48E-06	5.69E-06	5.89E-06	5.90E-06	5.31E-06
4	5.40E-06	5.71E-06	5.82E-06	6.12E-06	6.18E-06	6.30E-06	5.64E-06
5	5.03E-06	5.34E-06	5.50E-06	5.70E-06	5.85E-06	5.89E-06	5.29E-06
6	5.03E-06	5.38E-06	5.54E-06	5.71E-06	5.86E-06	5.98E-06	5.36E-06
7	5.42E-06	5.79E-06	5.92E-06	6.15E-06	6.30E-06	6.26E-06	5.75E-06
8	5.00E-06	5.33E-06	5.46E-06	5.67E-06	5.80E-06	5.85E-06	5.28E-06
9	5.24E-06	5.62E-06	5.77E-06	6.03E-06	6.35E-06	6.31E-06	5.70E-06
10	4.94E-06	5.28E-06	5.42E-06	5.65E-06	5.79E-06	5.79E-06	5.17E-06
22	5.09E-06	5.23E-06	5.27E-06	5.35E-06	5.20E-06	5.15E-06	4.87E-06
Biased Statistics							
Average Biased	5.10E-06	5.40E-06	5.62E-06	5.78E-06	5.92E-06	5.97E-06	5.37E-06
Std Dev Biased	2.01E-07	2.02E-07	2.38E-07	2.14E-07	1.62E-07	2.02E-07	1.64E-07
Ps90%/90% (+KTL) Biased	5.65E-06	5.96E-06	6.27E-06	6.37E-06	6.36E-06	6.52E-06	5.82E-06
Ps90%/90% (-KTL) Biased	4.54E-06	4.85E-06	4.96E-06	5.20E-06	5.48E-06	5.41E-06	4.92E-06
Un-Biased Statistics							
Average Un-Biased	5.12E-06	5.48E-06	5.62E-06	5.84E-06	6.02E-06	6.04E-06	5.45E-06
Std Dev Un-Biased	2.01E-07	2.17E-07	2.12E-07	2.33E-07	2.81E-07	2.38E-07	2.55E-07
Ps90%/90% (+KTL) Un-Biased	5.68E-06	6.07E-06	6.21E-06	6.48E-06	6.79E-06	6.69E-06	6.15E-06
Ps90%/90% (-KTL) Un-Biased	4.57E-06	4.88E-06	5.04E-06	5.20E-06	5.25E-06	5.38E-06	4.75E-06
Specification MIN	4.00E-06	4.40E-06	4.40E-06	4.40E-06	4.20E-06	4.20E-06	4.20E-06
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	1.00E-05	1.00E-05	1.00E-05	1.00E-05	1.05E-05	1.05E-05	1.05E-05
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

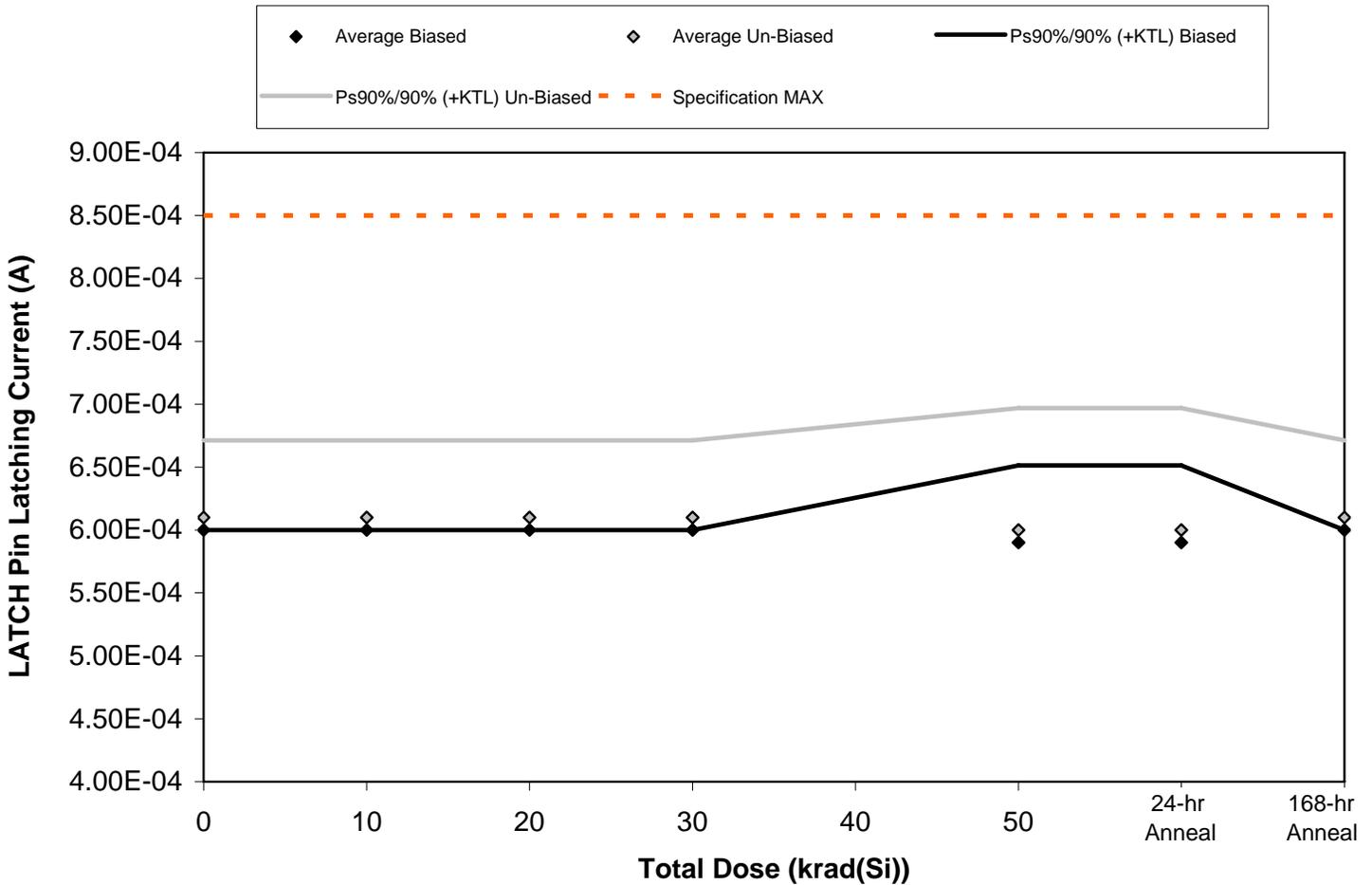


Figure 5.14. Plot of LATCH Pin Latching Current (A) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.14. Raw data for LATCH Pin Latching Current (A) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

LATCH Pin Latching Current (A)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
2	6.00E-04	6.00E-04	6.00E-04	6.00E-04	5.50E-04	5.50E-04	6.00E-04
3	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
4	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
5	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
6	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
7	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
8	6.50E-04	6.50E-04	6.50E-04	6.50E-04	6.50E-04	6.50E-04	6.50E-04
9	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
10	6.00E-04	6.00E-04	6.00E-04	6.00E-04	5.50E-04	5.50E-04	6.00E-04
22	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.00E-04
Biased Statistics							
Average Biased	6.00E-04	6.00E-04	6.00E-04	6.00E-04	5.90E-04	5.90E-04	6.00E-04
Std Dev Biased	0.00E+00	0.00E+00	0.00E+00	0.00E+00	2.24E-05	2.24E-05	0.00E+00
Ps90%/90% (+KTL) Biased	6.00E-04	6.00E-04	6.00E-04	6.00E-04	6.51E-04	6.51E-04	6.00E-04
Ps90%/90% (-KTL) Biased	6.00E-04	6.00E-04	6.00E-04	6.00E-04	5.29E-04	5.29E-04	6.00E-04
Un-Biased Statistics							
Average Un-Biased	6.10E-04	6.10E-04	6.10E-04	6.10E-04	6.00E-04	6.00E-04	6.10E-04
Std Dev Un-Biased	2.24E-05	2.24E-05	2.24E-05	2.24E-05	3.54E-05	3.54E-05	2.24E-05
Ps90%/90% (+KTL) Un-Biased	6.71E-04	6.71E-04	6.71E-04	6.71E-04	6.97E-04	6.97E-04	6.71E-04
Ps90%/90% (-KTL) Un-Biased	5.49E-04	5.49E-04	5.49E-04	5.49E-04	5.03E-04	5.03E-04	5.49E-04
Specification MAX	8.50E-04	8.50E-04	8.50E-04	8.50E-04	8.50E-04	8.50E-04	8.50E-04
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

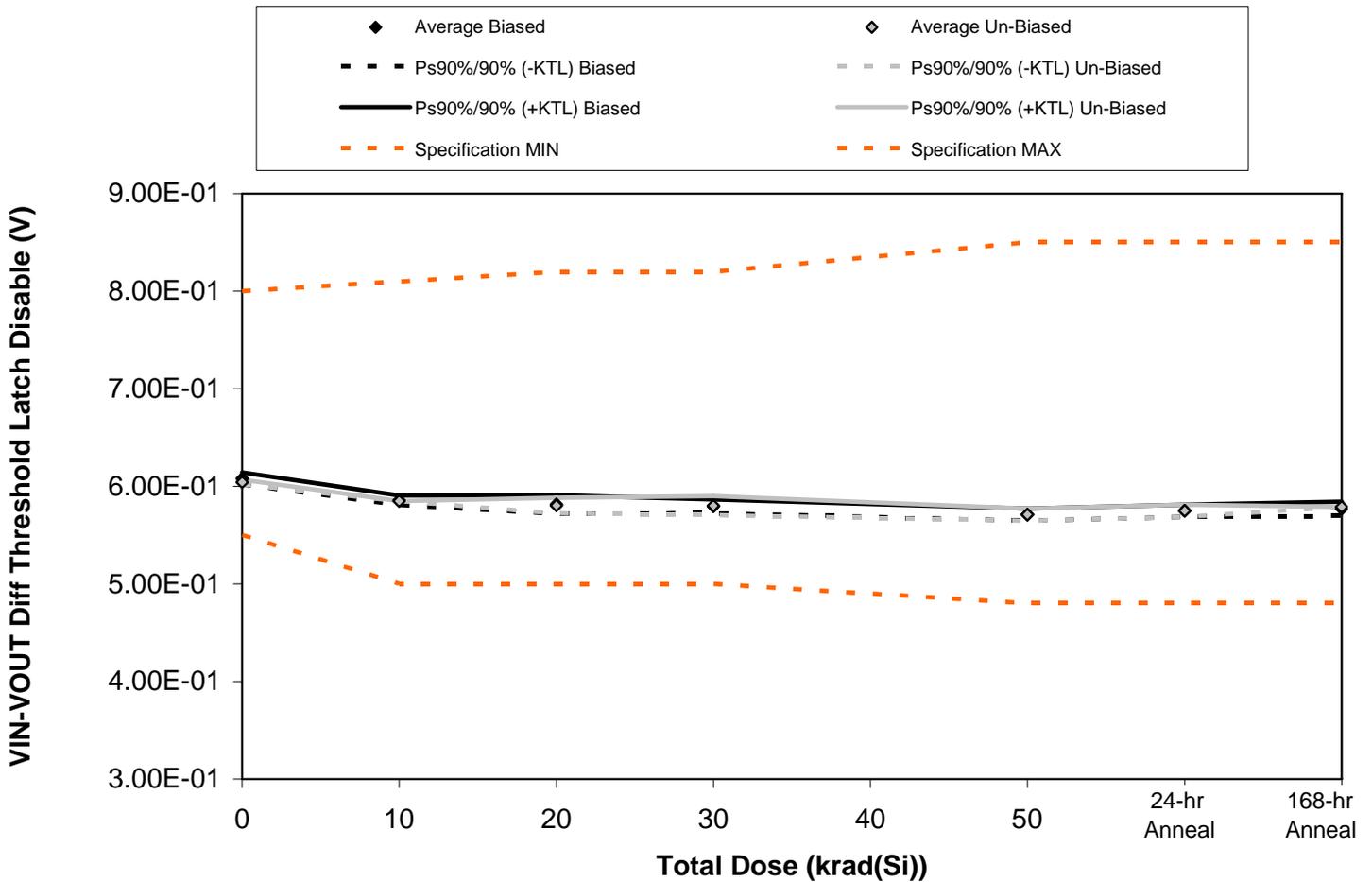


Figure 5.15. Plot of VIN-VOUT Diff Threshold Latch Disable (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.15. Raw data for VIN-VOUT Diff Threshold Latch Disable (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

VIN-VOUT Diff Threshold Latch Disable (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	6.09E-01	5.85E-01	5.85E-01	5.79E-01	5.70E-01	5.74E-01	5.74E-01
2	6.09E-01	5.85E-01	5.80E-01	5.79E-01	5.70E-01	5.74E-01	5.79E-01
3	6.04E-01	5.85E-01	5.77E-01	5.77E-01	5.70E-01	5.74E-01	5.74E-01
4	6.09E-01	5.85E-01	5.80E-01	5.79E-01	5.70E-01	5.74E-01	5.79E-01
5	6.09E-01	5.89E-01	5.85E-01	5.84E-01	5.75E-01	5.79E-01	5.79E-01
6	6.04E-01	5.85E-01	5.80E-01	5.77E-01	5.70E-01	5.74E-01	5.79E-01
7	6.04E-01	5.85E-01	5.80E-01	5.77E-01	5.70E-01	5.74E-01	5.79E-01
8	6.04E-01	5.85E-01	5.80E-01	5.84E-01	5.70E-01	5.74E-01	5.79E-01
9	6.04E-01	5.85E-01	5.77E-01	5.79E-01	5.70E-01	5.74E-01	5.79E-01
10	6.06E-01	5.85E-01	5.85E-01	5.84E-01	5.75E-01	5.79E-01	5.79E-01
22	6.04E-01	5.89E-01	5.90E-01	5.89E-01	5.80E-01	5.84E-01	5.89E-01
Biased Statistics							
Average Biased	6.08E-01	5.86E-01	5.81E-01	5.80E-01	5.71E-01	5.75E-01	5.77E-01
Std Dev Biased	2.24E-03	1.79E-03	3.51E-03	2.61E-03	2.24E-03	2.24E-03	2.74E-03
Ps90%/90% (+KTL) Biased	6.14E-01	5.91E-01	5.91E-01	5.87E-01	5.77E-01	5.81E-01	5.85E-01
Ps90%/90% (-KTL) Biased	6.02E-01	5.81E-01	5.72E-01	5.72E-01	5.65E-01	5.69E-01	5.69E-01
Un-Biased Statistics							
Average Un-Biased	6.04E-01	5.85E-01	5.80E-01	5.80E-01	5.71E-01	5.75E-01	5.79E-01
Std Dev Un-Biased	8.94E-04	0.00E+00	2.88E-03	3.56E-03	2.24E-03	2.24E-03	0.00E+00
Ps90%/90% (+KTL) Un-Biased	6.07E-01	5.85E-01	5.88E-01	5.90E-01	5.77E-01	5.81E-01	5.79E-01
Ps90%/90% (-KTL) Un-Biased	6.02E-01	5.85E-01	5.73E-01	5.70E-01	5.65E-01	5.69E-01	5.79E-01
Specification MIN	5.50E-01	5.00E-01	5.00E-01	5.00E-01	4.80E-01	4.80E-01	4.80E-01
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS
Specification MAX	8.00E-01	8.10E-01	8.20E-01	8.20E-01	8.50E-01	8.50E-01	8.50E-01
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS

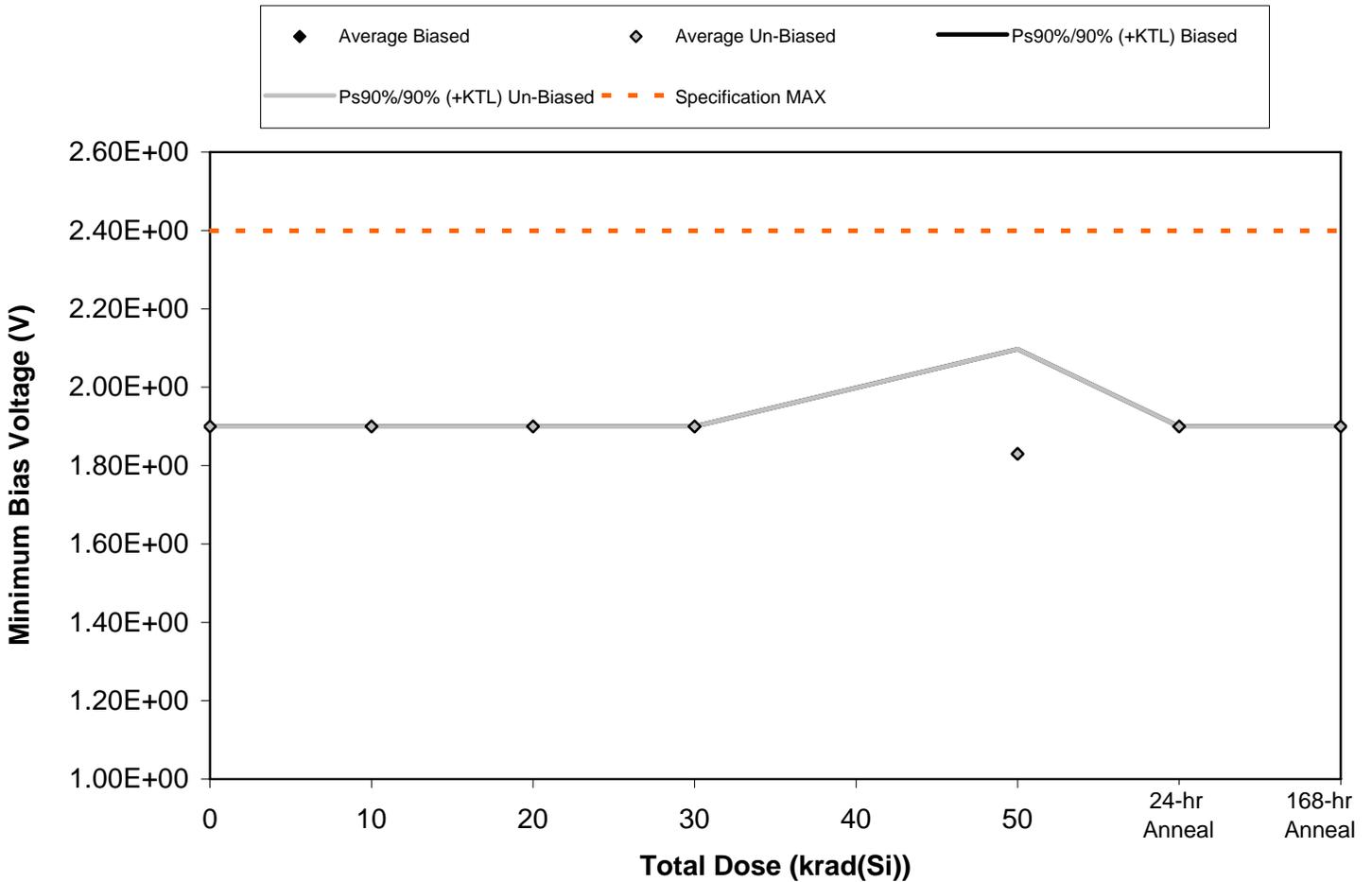


Figure 5.16. Plot of Minimum Bias Voltage (V) versus total dose. The data show no significant change with total dose. The solid diamonds are the average of the measured data points for the samples irradiated under electrical bias while the shaded diamonds are the average of the measured data points for the samples irradiated with all pins tied to ground. The black lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated under electrical bias while the gray lines (solid and/or dashed) are the average of the data points after application of the KTL statistics on the samples irradiated in the unbiased condition. The red dotted line(s) are the pre- and/or post-irradiation minimum and/or maximum specification value as defined in the datasheet and/or test plan.



Table 5.16. Raw data for Minimum Bias Voltage (V) versus total dose, including the statistical analysis, specification and the status of the testing (pass/fail).

Minimum Bias Voltage (V)	Total Dose (krad(Si))					24 hr Anneal	168 hr Anneal
	0	10	20	30	50		
Device							
1	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.75E+00	1.90E+00	1.90E+00
2	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.70E+00	1.90E+00	1.90E+00
3	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
4	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
5	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
6	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.70E+00	1.90E+00	1.90E+00
7	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
8	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
9	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.75E+00	1.90E+00	1.90E+00
10	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
22	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.90E+00
Biased Statistics							
Average Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.83E+00	1.90E+00	1.90E+00
Std Dev Biased	0.00E+00	0.00E+00	0.00E+00	0.00E+00	9.75E-02	0.00E+00	0.00E+00
Ps90%/90% (+KTL) Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	2.10E+00	1.90E+00	1.90E+00
Ps90%/90% (-KTL) Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.56E+00	1.90E+00	1.90E+00
Un-Biased Statistics							
Average Un-Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.83E+00	1.90E+00	1.90E+00
Std Dev Un-Biased	0.00E+00	0.00E+00	0.00E+00	0.00E+00	9.75E-02	0.00E+00	0.00E+00
Ps90%/90% (+KTL) Un-Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	2.10E+00	1.90E+00	1.90E+00
Ps90%/90% (-KTL) Un-Biased	1.90E+00	1.90E+00	1.90E+00	1.90E+00	1.56E+00	1.90E+00	1.90E+00
Specification MAX	2.40E+00	2.40E+00	2.40E+00	2.40E+00	2.40E+00	2.40E+00	2.40E+00
Status	PASS	PASS	PASS	PASS	PASS	PASS	PASS



6.0. Summary / Conclusions

The low dose rate total ionizing dose testing described in this final report was performed using the facilities at Radiation Assured Devices' Longmire Laboratories in Colorado Springs, CO. For the low dose rate ELDRS testing described in this report, the devices were placed approximately 2-meters from the Co-60 rods to achieve the required 10mrads(Si)/s dose rate. Samples of the RH1573MJ8 low dropout PNP regulator driver described in this report were irradiated biased with a single 7V V_{IN} and unbiased (all leads tied to ground). The devices were irradiated to a maximum total ionizing dose level of 50krads(Si) with a pre-rad baseline reading as well as incremental readings at 10, 20, and 30krads(Si). Electrical testing occurred within one hour following the end of each irradiation segment. For intermediate irradiations, the units were tested and returned to total dose exposure within two hours from the end of the previous radiation increment. In addition, all units-under-test received a 24hr room temperature and 168hr 100°C anneal, using the same bias conditions as the radiation exposure.

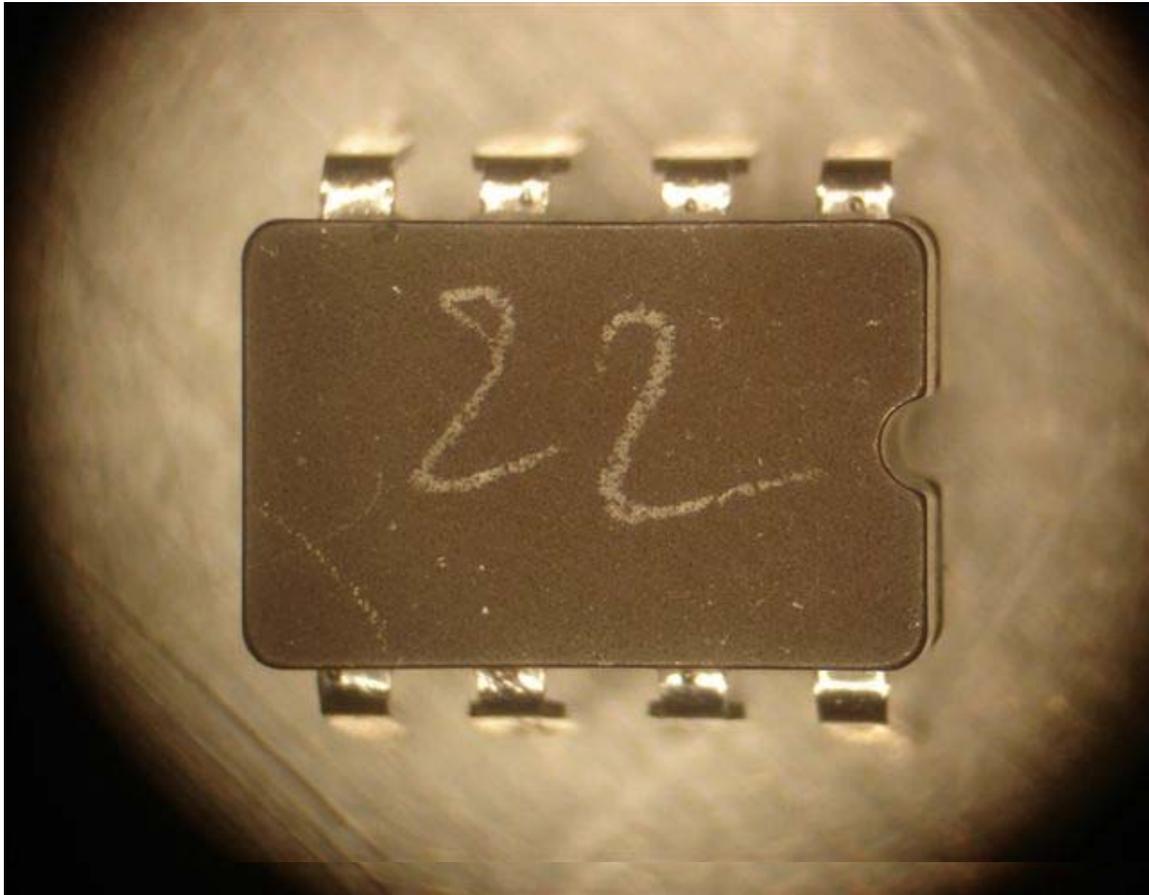
The parametric data was obtained as "read and record" and all the raw data plus an attributes summary were presented in this report. The attributes data contains the average, standard deviation and the average with the KTL values applied. The KTL value used was 2.742 per MIL HDBK 814 using one-sided tolerance limits of 99/90 and a 5-piece sample size. Note that the following criteria was used to determine the outcome of the testing: following the radiation exposure each parameter had to pass the specification value and the average value for the ten-piece sample must pass the specification value when the KTL limits are applied. If these conditions were not both satisfied following the radiation exposure, then the lot would be logged as an RLAT failure.

Using the conditions stated above, the RH1573MJ8 devices passed the ELDRS test to 50krads(Si) with no significant degradation to most of the measured parameters. Where radiation induced degradation was observed the degradation was not sufficient to cause the parameter to exceed the specification value. Note that V_{REF} exceeded the upper datasheet specification after application of the 90/90 KTL statistics due to the relative large standard deviation of the sample population compared to the very tight specification limits. In our opinion this lot of material could be qualified to 50krads(Si) using larger samples sizes and an "attributes" approach, i.e. 22 units passing with 0 failures.



Appendix A: Photograph of device-under-test to show part markings

Note: RH1573K DICE is assembled in CERDIP-8 package for testing purposes.





Appendix B: Radiation Bias Connections

Biased Samples:

Pin	Function	Connection / Bias
1	FB	GND
2	LATCH	GND
3	SHDN	GND
4	GND	GND
5	DRIVE	To Pin 6 via 340Ω Resistor
6	VIN	To 7V using 1μF decoupling, to Pin 5 via 340Ω Resistor
7	VOUT	NC
8	COMP	NC

Unbiased Samples:

Pin	Function	Connection / Bias
1	FB	GND
2	LATCH	GND
3	SHDN	GND
4	GND	GND
5	DRIVE	GND
6	VIN	GND
7	VOUT	GND
8	COMP	GND

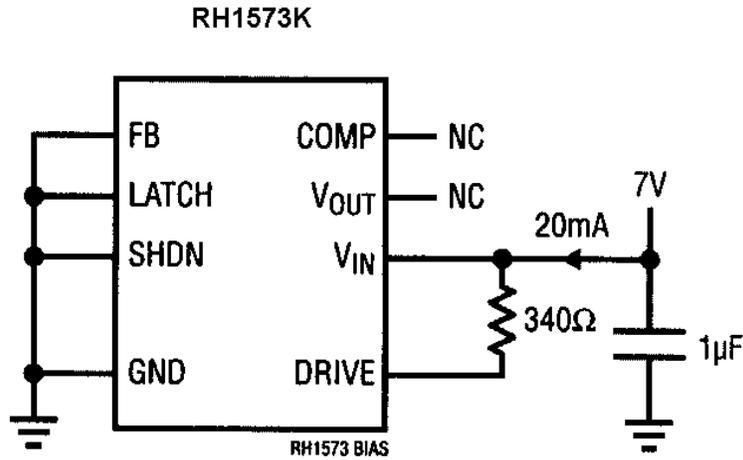


Figure B.1. Irradiation bias circuit for the units to be irradiated under electrical bias. This figure was extracted from LINEAR TECHNOLOGY CORPORATION, RH1573K Drawing number 05-08-5223.

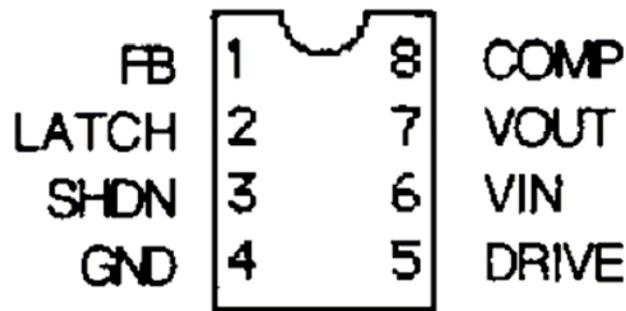


Figure B.2. Package drawing (for reference only). This figure was extracted from LINEAR TECHNOLOGY CORPORATION, RH1573K Drawing number 05-08-5223.



Appendix C: Electrical Test Parameters and Conditions

All electrical tests for this device are performed on one of Radiation Assured Device's LTS2020 Test Systems. The LTS2020 Test System is a programmable parametric tester that provides parameter measurements for a variety of digital, analog and mixed signal products including voltage regulators, voltage comparators, D to A and A to D converters. The LTS2020 Test System achieves accuracy and sensitivity through the use of software self-calibration and an internal relay matrix with separate family boards and custom personality adapter boards. The tester uses this relay matrix to connect the required test circuits, select the appropriate voltage / current sources and establish the needed measurement loops for all the tests performed. The tests will be conducted using the LTS-2510 Digital Family Board, and the RH1573/LT1573 BGSS-080908 DUT board. The measured parameters and test conditions are shown in Table C.1.

A listing of the measurement precision/resolution for each parameter is shown in Tables C.2. The precision/resolution values were obtained either from test data or from the DAC resolution of the LTS-2020. To generate the precision/resolution shown in Table C.2, one of the units-under-test was tested repetitively (a total of 10-times with re-insertion between tests) to obtain the average test value and standard deviation. Using this test data MIL-HDBK-814 90/90 KTL statistics were applied to the measured standard deviation to generate the final measurement range. This value encompasses the precision/resolution of all aspects of the test system, including the LTS2020 mainframe, family board, socket assembly and DUT board as well as insertion error. In some cases, the measurement resolution is limited by the internal DACs, which results in a measured standard deviation of zero. In these instances the precision/resolution will be reported back as the LSB of the DAC.

Note that the testing and statistics used in this document are based on an "analysis of variables" technique, which relies on small sample sizes to qualify much larger lot sizes (see MIL-HDBK-814, p. 91 for a discussion of statistical treatments). Not all measured parameters are well suited to this approach due to inherent large variations. If necessary, larger samples sizes could be used to qualify these parameters using an "attributes" approach.



Table C.1. Measured parameters and test conditions for the RH1573MJ8

TEST DESCRIPTION	TEST CONDITIONS
Input Quiescent Current (A)	$V_{IN}=7V$
Reference Voltage (V)	$I_{DRIVE}=20mA$
Line Regulation (V)	$I_{DRIVE}=20mA, V_{IN}=3V-7V$
Load Regulation (V)	$I_{DRIVE}=20mA-250mA$
FB Pin Bias Current (A)	$V_{FB}=1.265V$
DRIVE Pin Current $V_{FB}=1.35V$ (A)	$V_{FB}=1.35V, V_{DRIVE}=7V$
DRIVE Pin Current $V_{FB}=1.15V$ (A)	$V_{FB}=1.15V, V_{DRIVE}=1.5V$
DRIVE Pin Saturation Voltage $I_D=20mA$ (V)	$I_{DRIVE}=20mA, V_{FB}=1.15V$
DRIVE Pin Saturation Voltage $I_D=250mA$ (V)	$I_{DRIVE}=250mA, V_{FB}=1.15V$
SHDN Pin Threshold Voltage (V)	$I_{DRIVE}=20mA, V_{IN}=5V$
SHDN Pin Current (A)	$V_{SHDN}=5V$
LATCH Pin Latch-Off Threshold Voltage (V)	$I_{DRIVE}=20mA, V_{IN}=5V$
LATCH Pin Charging Current (A)	
LATCH Pin Latching Current (A)	
VIN-VOUT Diff Threshold Latch Disable (V)	$V_{IN}=5V$
Minimum Bias Voltage (V)	



Table C.2 Measured parameters, pre-irradiation specifications and measurement resolutions for the RH1573MJ8

Measured Parameter	Pre-Irradiation Specification	Measurement Resolution/Precision
Input Quiescent Current (A)	2.8mA MAX	± 4.22E-06A
Reference Voltage (V)	1.252V-1.278V	± 8.71E-04V
Line Regulation (V)	2mV MAX	± 3.06E-04V
Load Regulation (V)	18mV MAX	± 1.12E-03V
FB Pin Bias Current (A)	4µA MAX	± 1.12E-08A
DRIVE Pin Current VFB=1.35V (A)	1.2mA MAX	± 9.97E-07A
DRIVE Pin Current VFB=1.15V (A)	290mA MIN	± 6.65E-04A
DRIVE Pin Saturation Voltage ID=20mA (V)	0.2V MAX	± 6.53E-04V
DRIVE Pin Saturation Voltage ID=250mA (V)	1V MAX	± 2.23E-03V
SHDN Pin Threshold Voltage (V)	1V-1.5V	± 1.00E-03V
SHDN Pin Current (A)	300µA MAX	± 2.61E-07A
LATCH Pin Latch-Off Threshold Voltage (V)	1.1V-1.8V	± 8.43E-03V
LATCH Pin Charging Current (A)	4µA-10µA	± 2.06E-08A
LATCH Pin Latching Current (A)	0.85mA MAX	± 5.00E-05A
VIN-VOUT Diff Threshold Latch Disable (V)	0.55V-0.8V	± 1.96E-03V
Minimum Bias Voltage (V)	2.4V MIN	± 1.00E-03V



Appendix D: List of Figures Used in Section 5 (ELDRS Test Results)

- 5.1 Input Quiescent Current (A)
- 5.2 Reference Voltage (V)
- 5.3 Line Regulation (V)
- 5.4 Load Regulation (V)
- 5.5 FB Pin Bias Current (A)
- 5.6 DRIVE Pin Current VFB=1.35V (A)
- 5.7 DRIVE Pin Current VFB=1.15V (A)
- 5.8 DRIVE Pin Saturation Voltage ID=20mA (V)
- 5.9 DRIVE Pin Saturation Voltage ID=250mA (V)
- 5.10 SHDN Pin Threshold Voltage (V)
- 5.11 SHDN Pin Current (A)
- 5.12 LATCH Pin Latch-Off Threshold Voltage (V)
- 5.13 LATCH Pin Charging Current (A)
- 5.14 LATCH Pin Latching Current (A)
- 5.15 VIN-VOOUT Diff Threshold Latch Disable (V)
- 5.16 Minimum Bias Voltage (V)